

“Characterization of SiPMs using Radiation Sources for Quantum Random Number Generation”



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Master Thesis



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QRNG

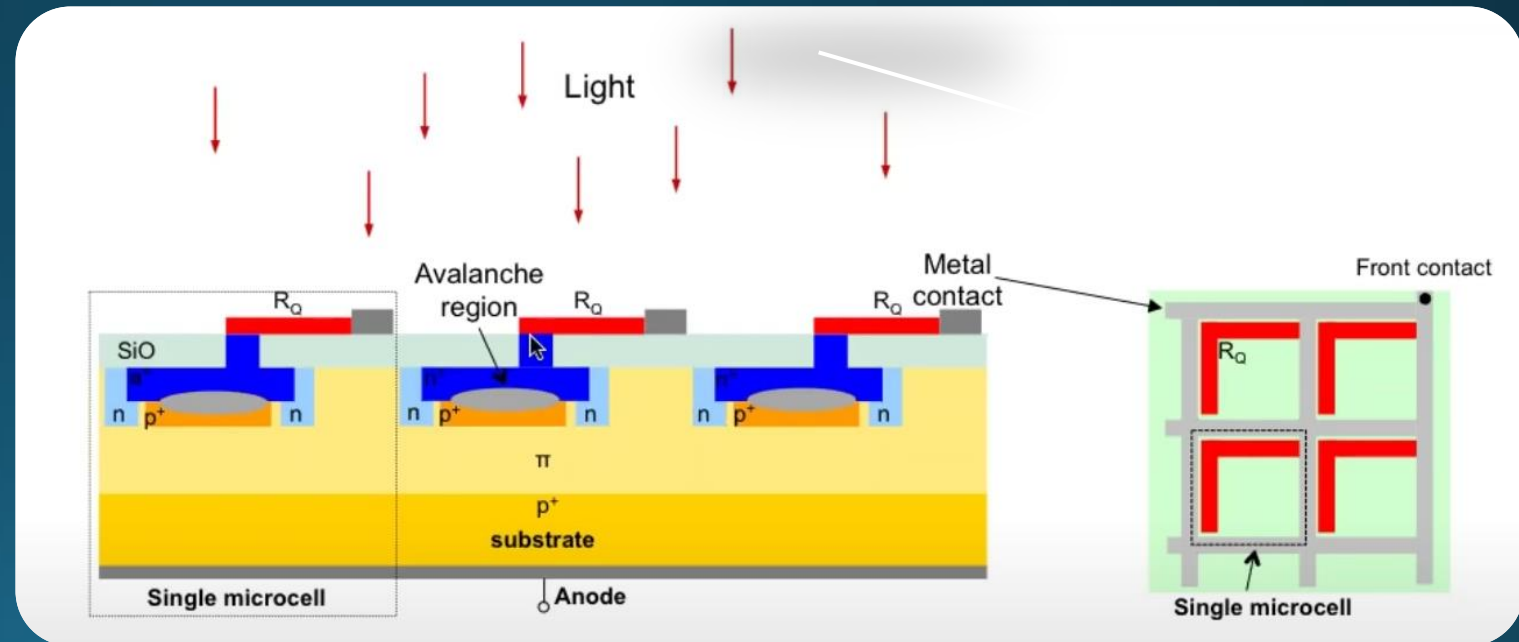
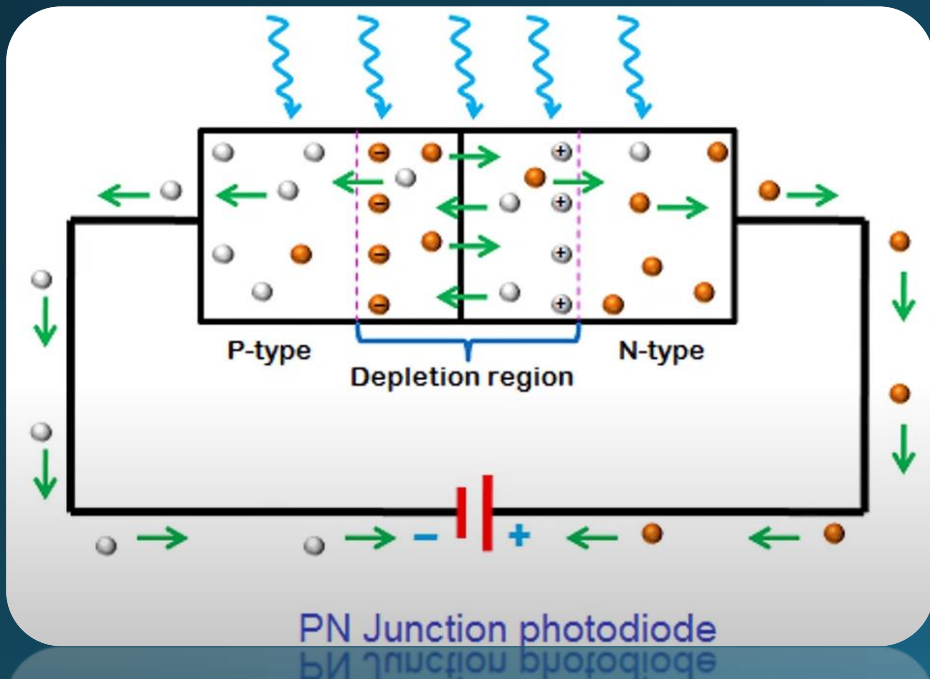
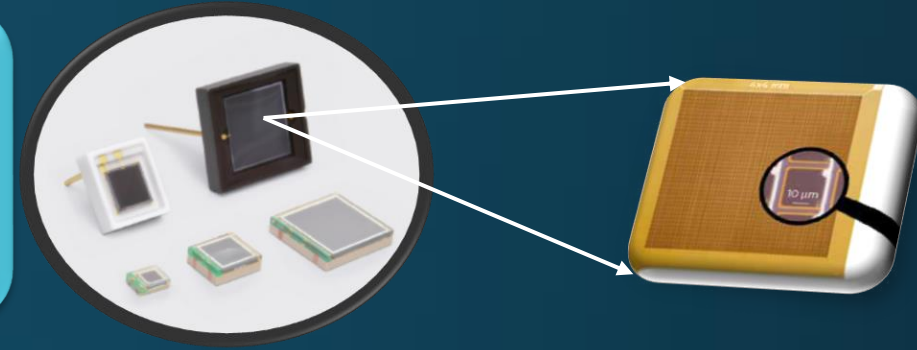
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SiPM Operating Principle

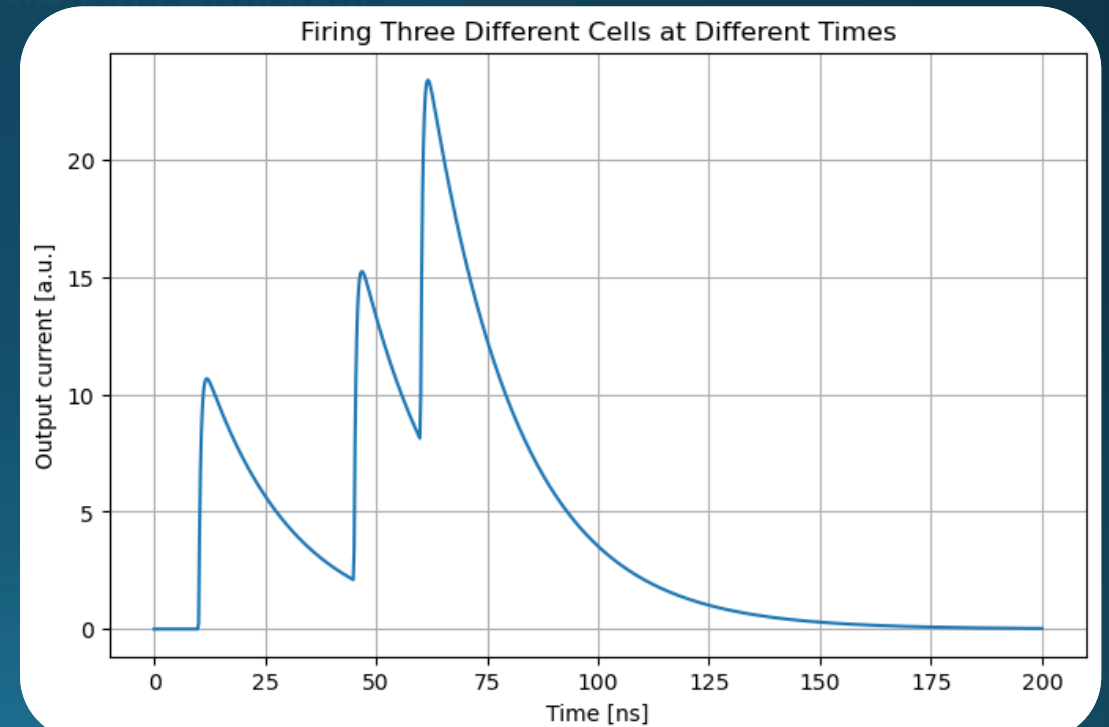
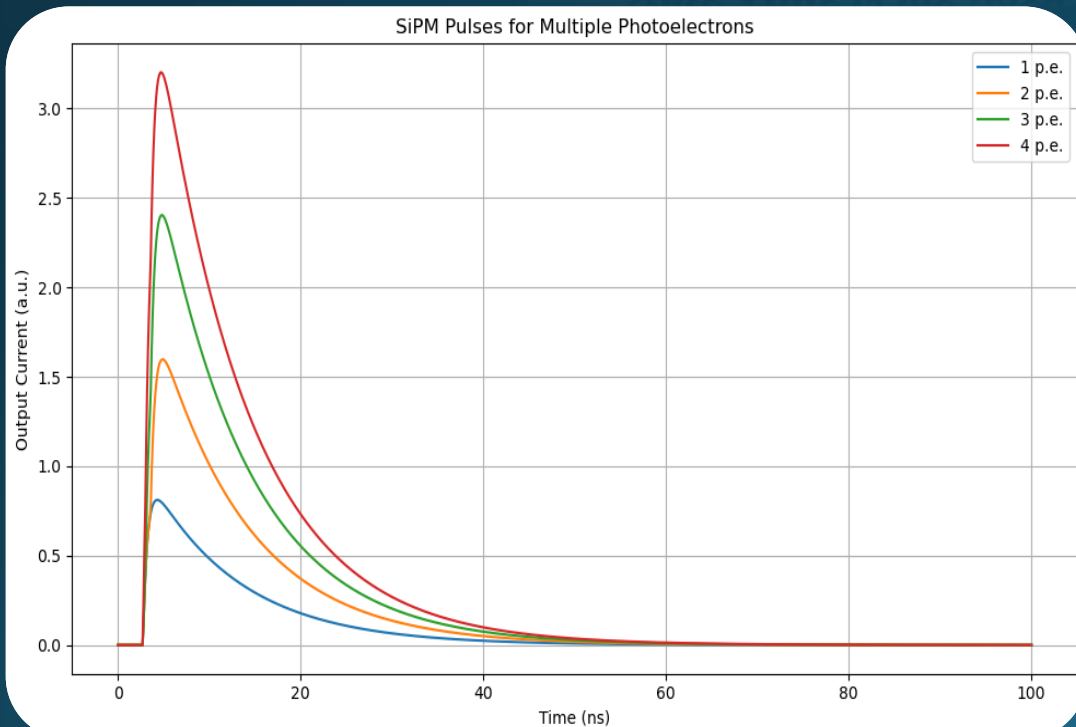
- Solid state PN Junction photodetector
- Produces current pulses of $\sim 10^6 e^-$ as response to absorption of a photon (Gain)
- Pixelated device
- Each pixel-microcell is an Avalanche photodiode (APD) connected in parallel
- Externally biased above breakdown voltage

- Photon Absorption
- Electron-Hole Pair Creation
- Avalanche Multiplication-Gain
- Pulse Generation by quenching
- Final Signal

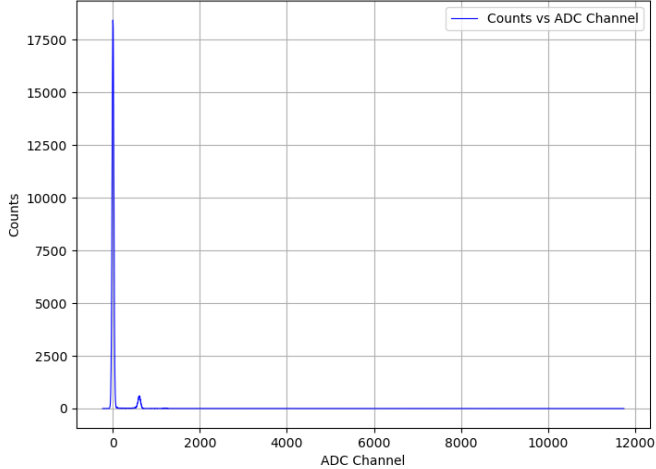


SiPM Signal

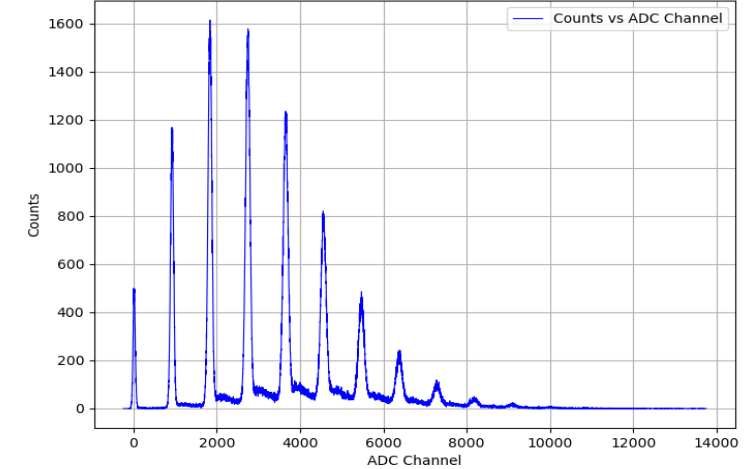
- The **final SiPM signal** corresponds to the **total output pulse**
- It is the **sum of the individual microcell pulses**
- Triggered either **simultaneously** or at **slightly different times**
- **Gate Time** is the fixed time window during which the detector **integrates the signal**



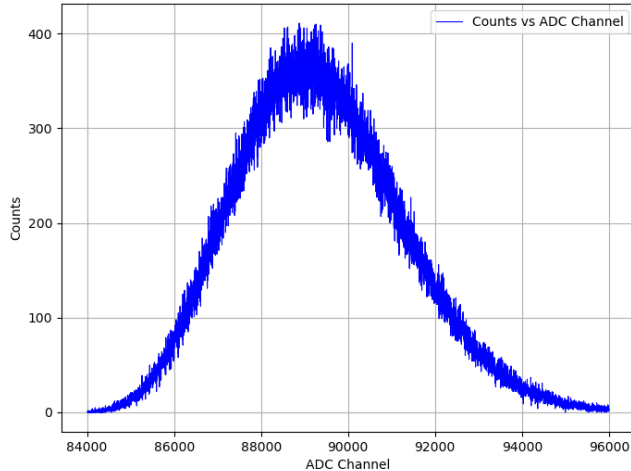
SiPM Photopeak Histogram - Zero Light Intensity



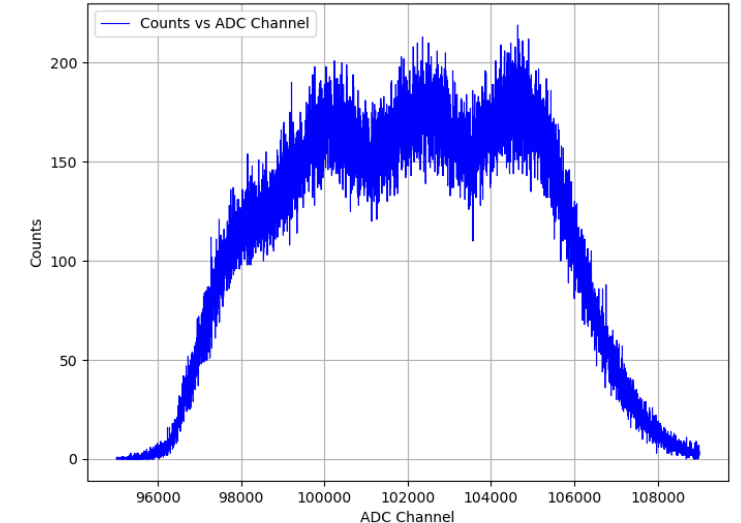
SiPM Photopeak Histogram - Medium Light Intensity



SiPM Photopeak Histogram - High Light Intensity



SiPM Photopeak Histogram - High Light Intensity



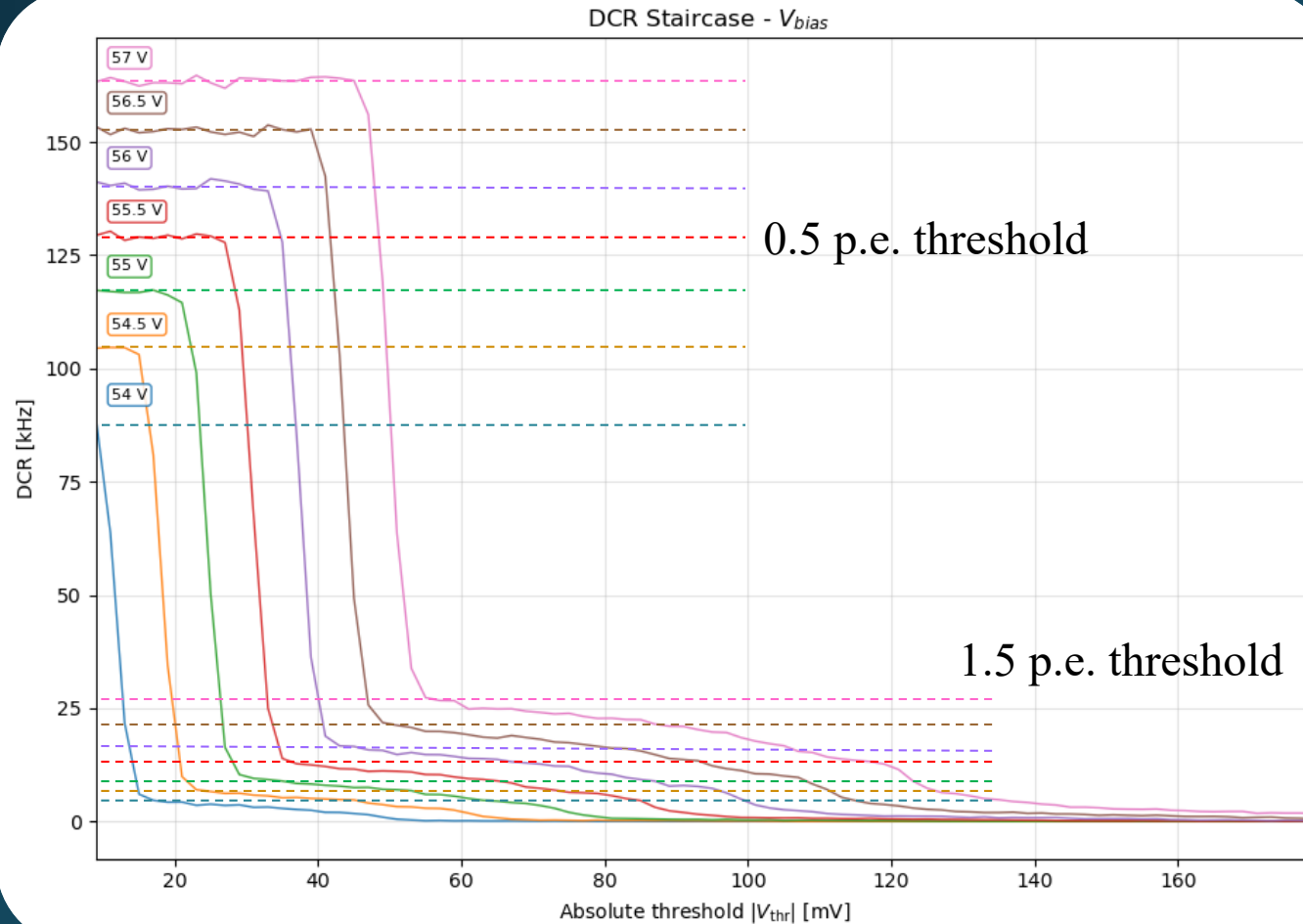
- **Photo-peaks** correspond to the **number of detected photons**
- **First peak** represents the baseline signal - pedestal (i.e., 0 detected photons)
- **The second peak** corresponds to **1 detected photon**, and so on
- **High Light Intensity** leads to **saturation**

saturation

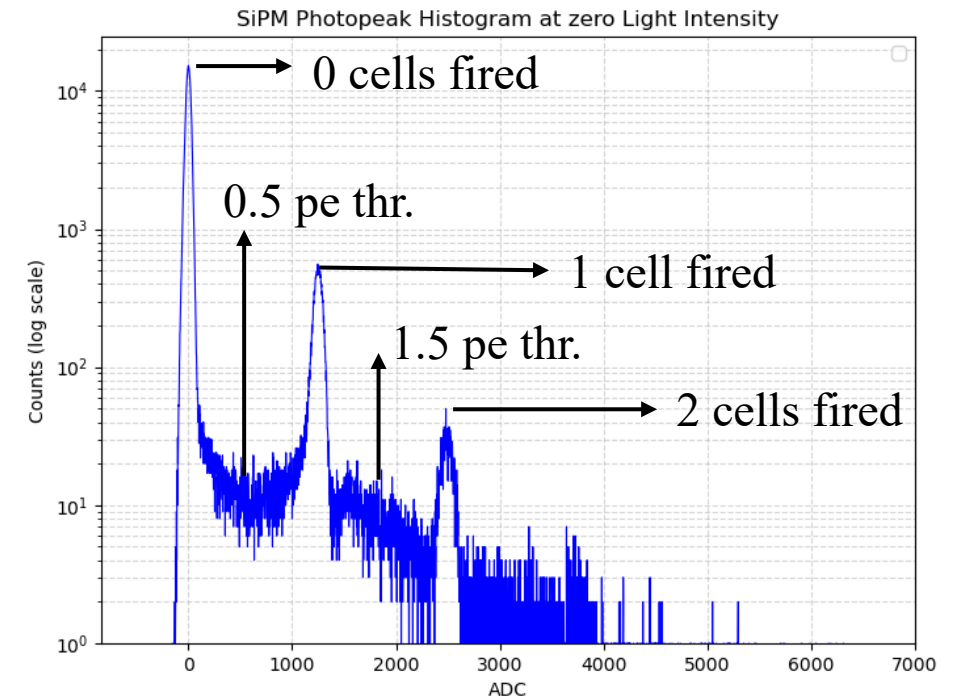
- **High Light Intensity** leads to **saturation**
- **The second peak** corresponds to **1 detected photon**, and so on
- **The second peak** corresponds to **1 detected photon**, and so on

Dark Counts Rate - DCR

The rate of spontaneous SiPM pulses occurring without incident light, caused by thermal carrier generation

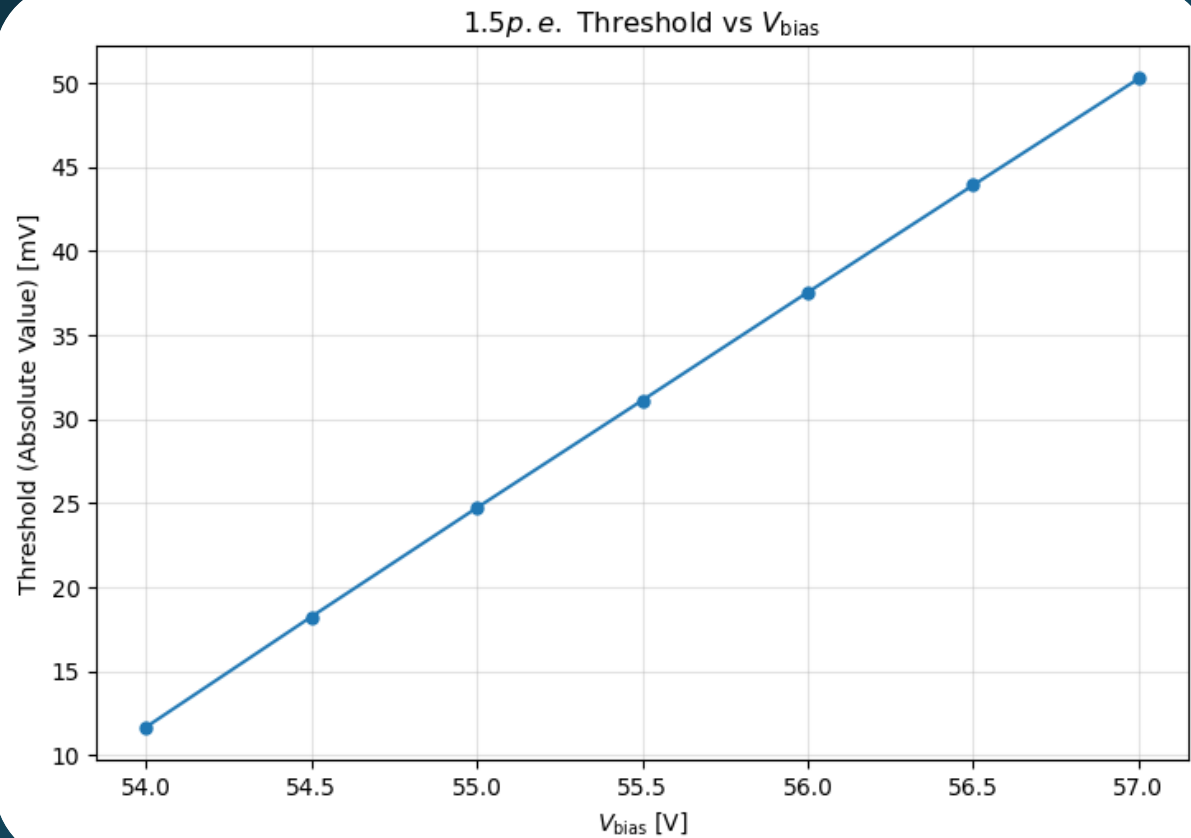


1.5 pe thr. : The discrimination level set halfway between the 1st and 2nd photo-peak to separate single cell's pulses from 2 cell's pulses

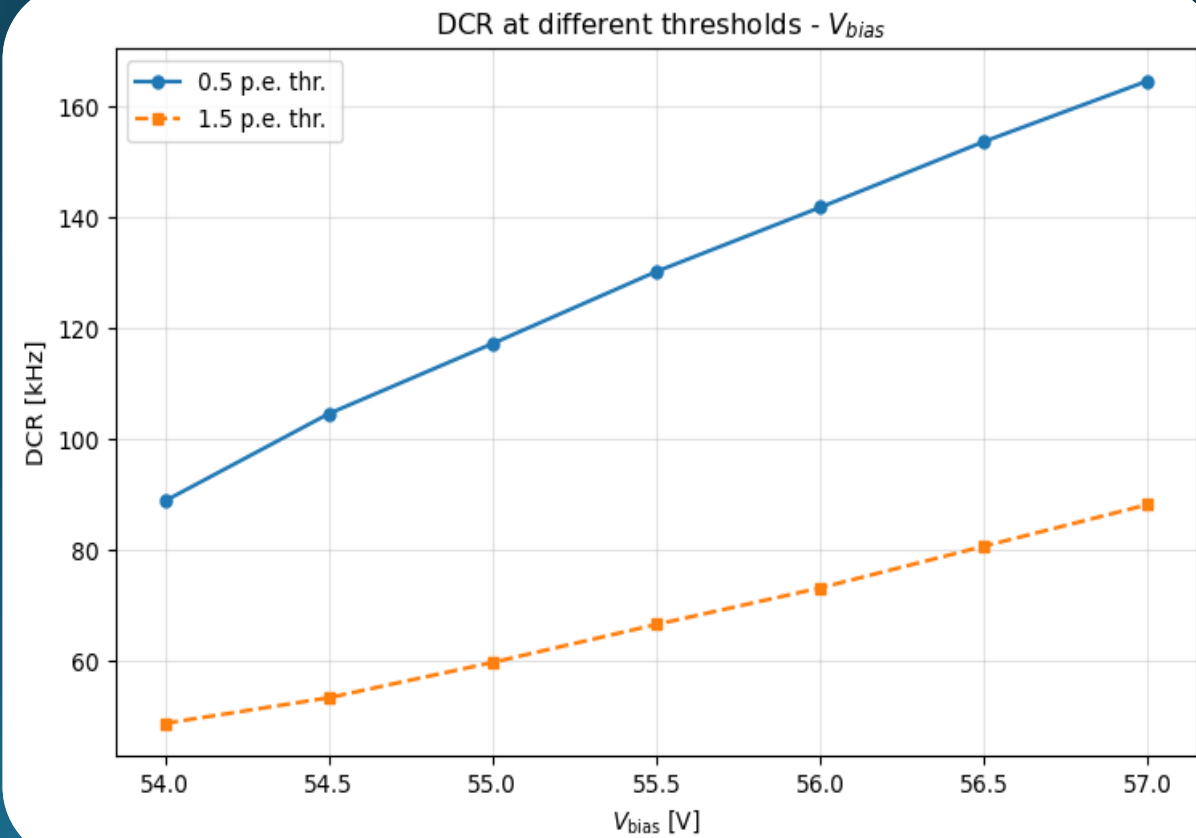


DCR - V_{bias}

1.5 p.e. Point per V_{bias}



$DCR_{0.5}$ and $DCR_{1.5}$

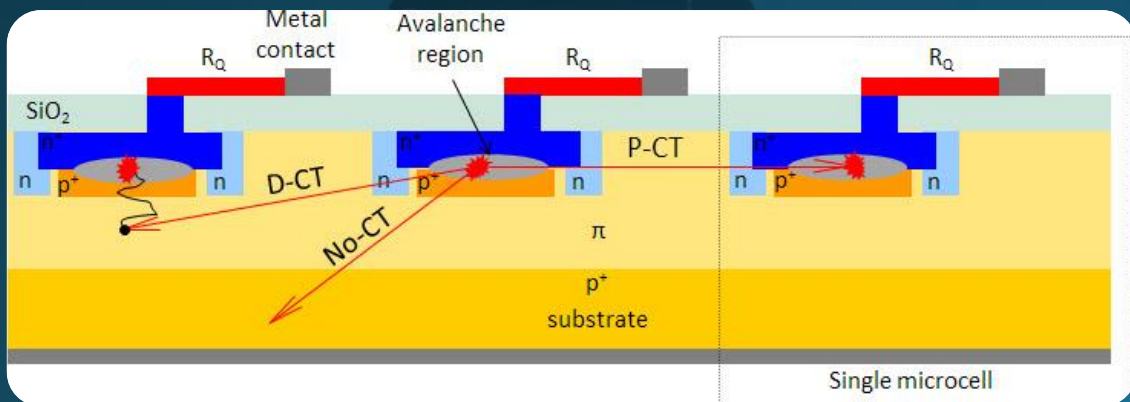
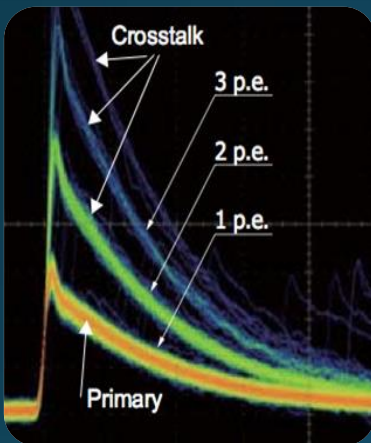


Optical Cross-Talk Probability

A single photon creates 1 p.e.-sized pulse

- **$DCR_{0.5}$: single cell's pulses included**
- **$DCR_{1.5}$: single cell's pulses not included**

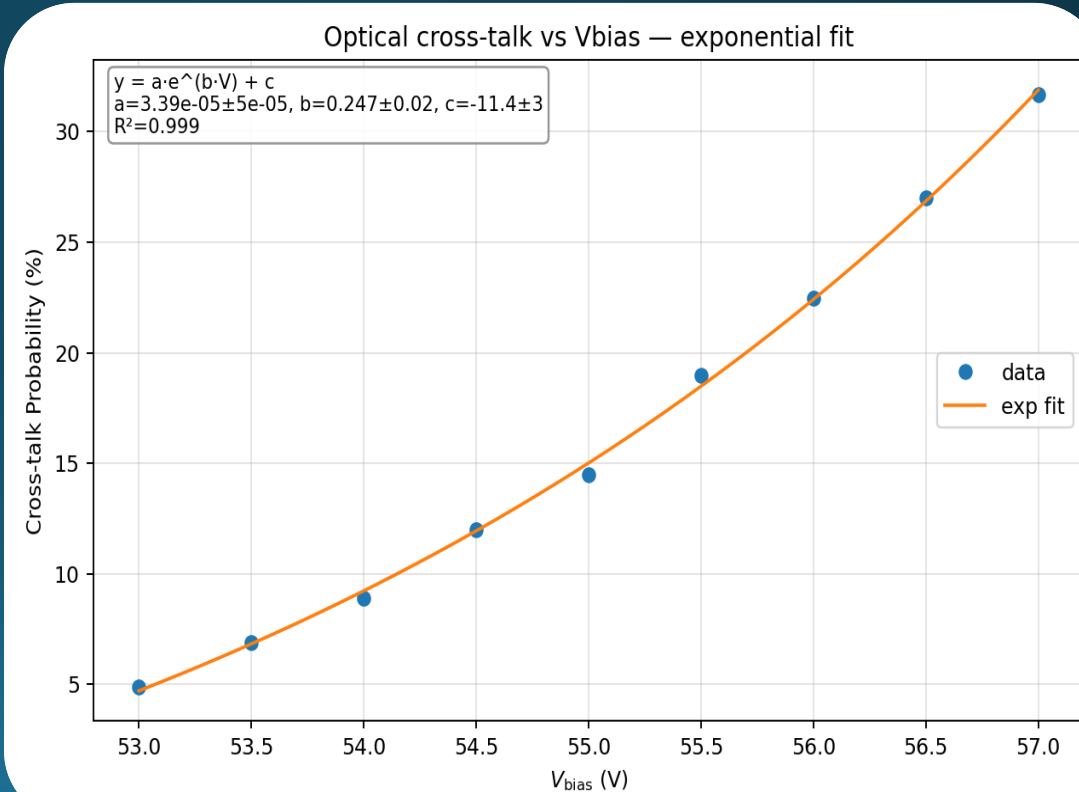
- $DCR_{0.5}$: single cell's pulses included
- $DCR_{1.5}$: single cell's pulses not included



Optical Cross-Talk: An avalanche in one microcell optically triggers a neighboring cell

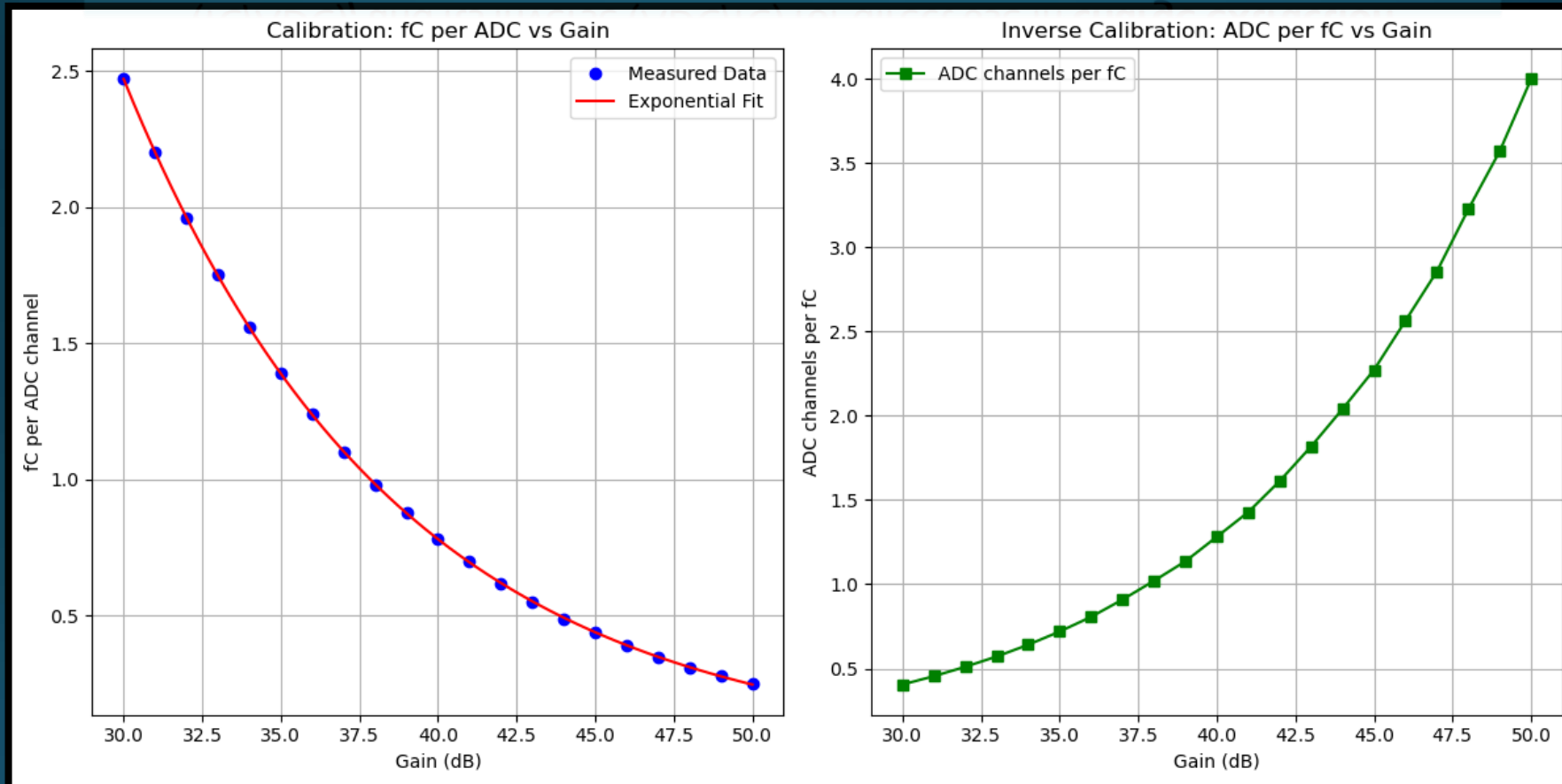
$$OCT = \frac{DCR_{1.5}}{DCR_{0.5}}$$

$$OCT = \frac{DCR_{1.5}}{DCR_{0.5}}$$



Digitizer Gain Calibration

These exponential fits describe the **gain-dependent conversion factor** (fC/ADC), and its inverse (ADC/fC) for direct use in **charge extraction**

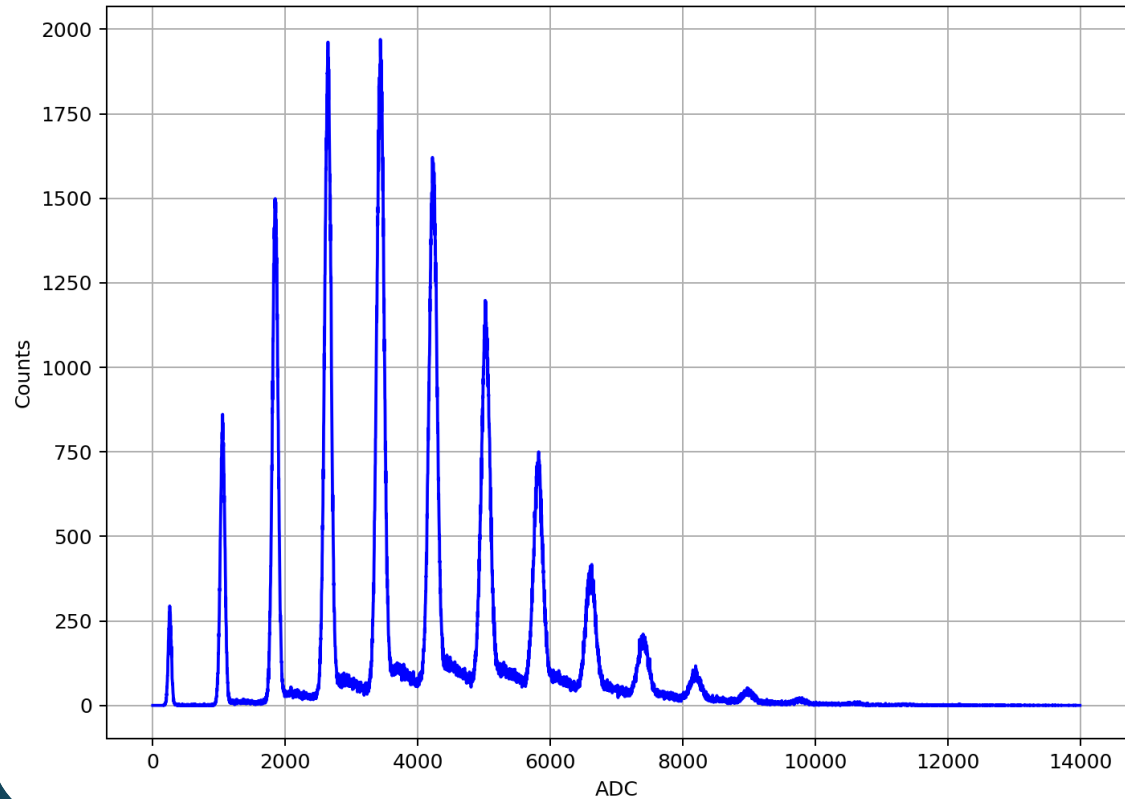


ADC to Charge transition

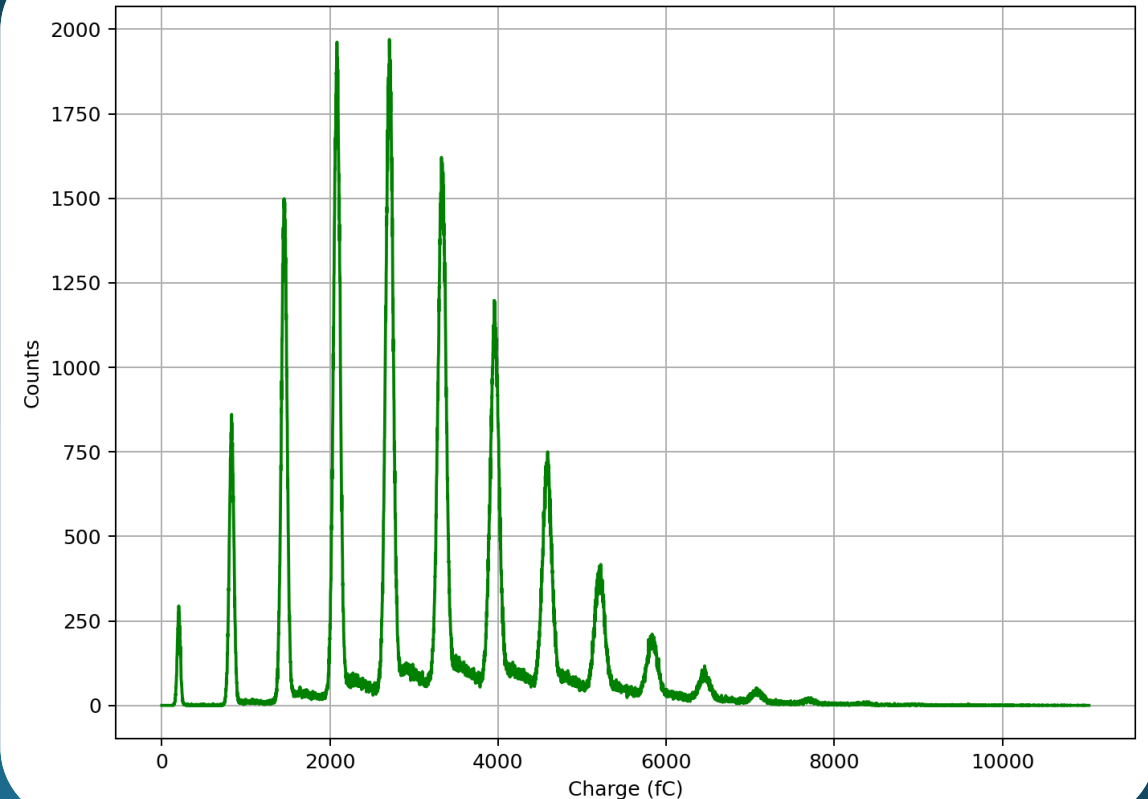
Example: Gain=40dB

$$fC/_{ADC} = 78.337 \cdot e^{(-0.115 \cdot 40)} + 0.001 \cong 0.788$$

V=53.6V.txt - Raw Data in ADC (shift=239.000 ADC)



V=53.6V.txt - Charge (fC)

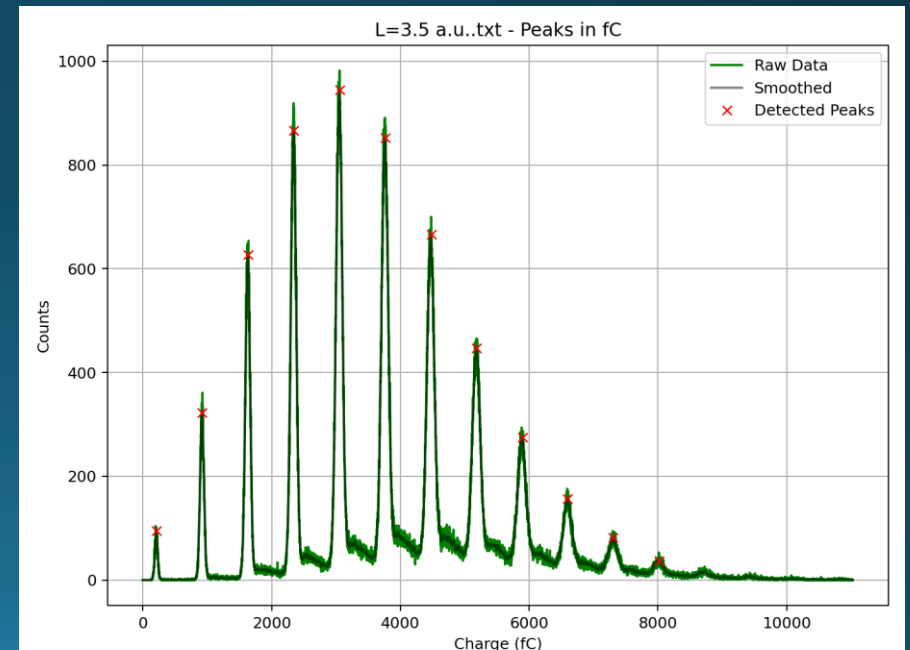
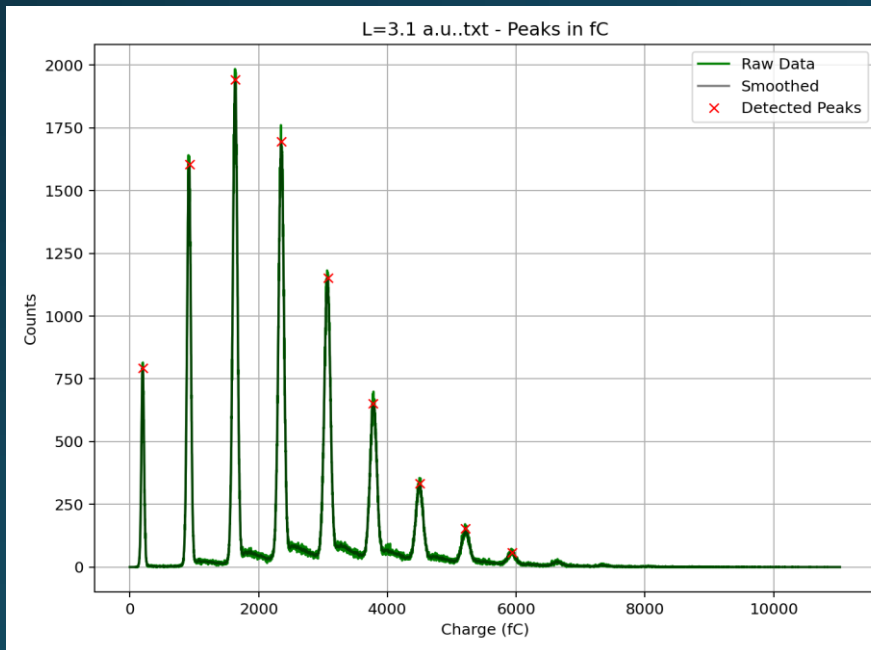
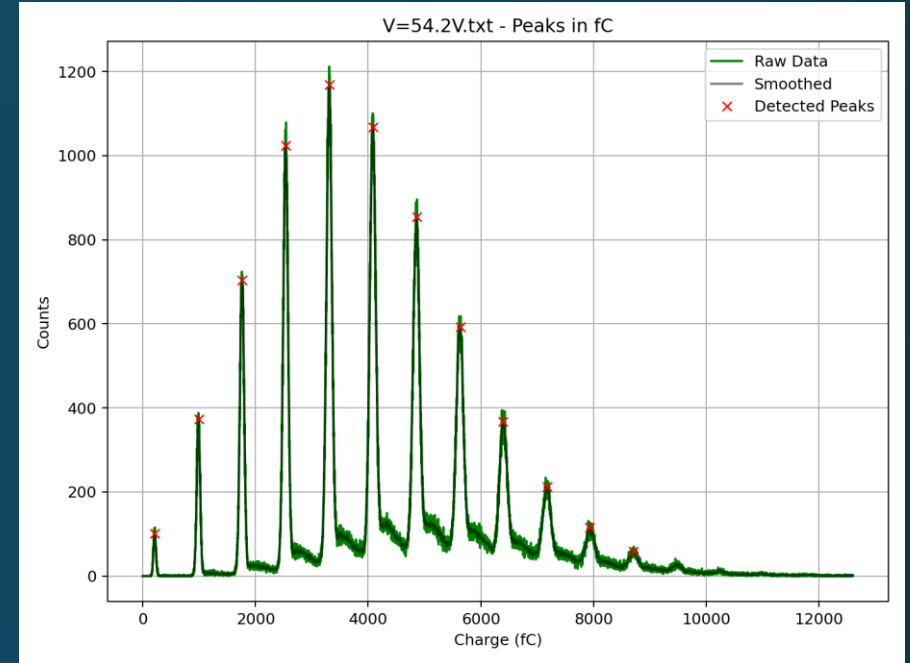
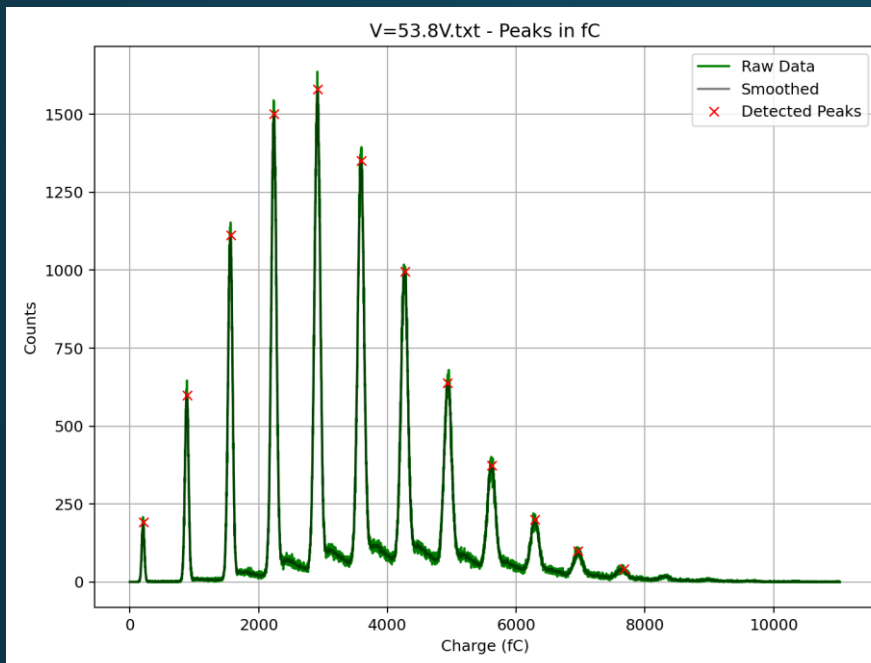


Constant Light
Intensity
-
Constant number
of peaks

of peaks
Constant number

Constant
 V_{bias}
-
Increasing
number of peaks

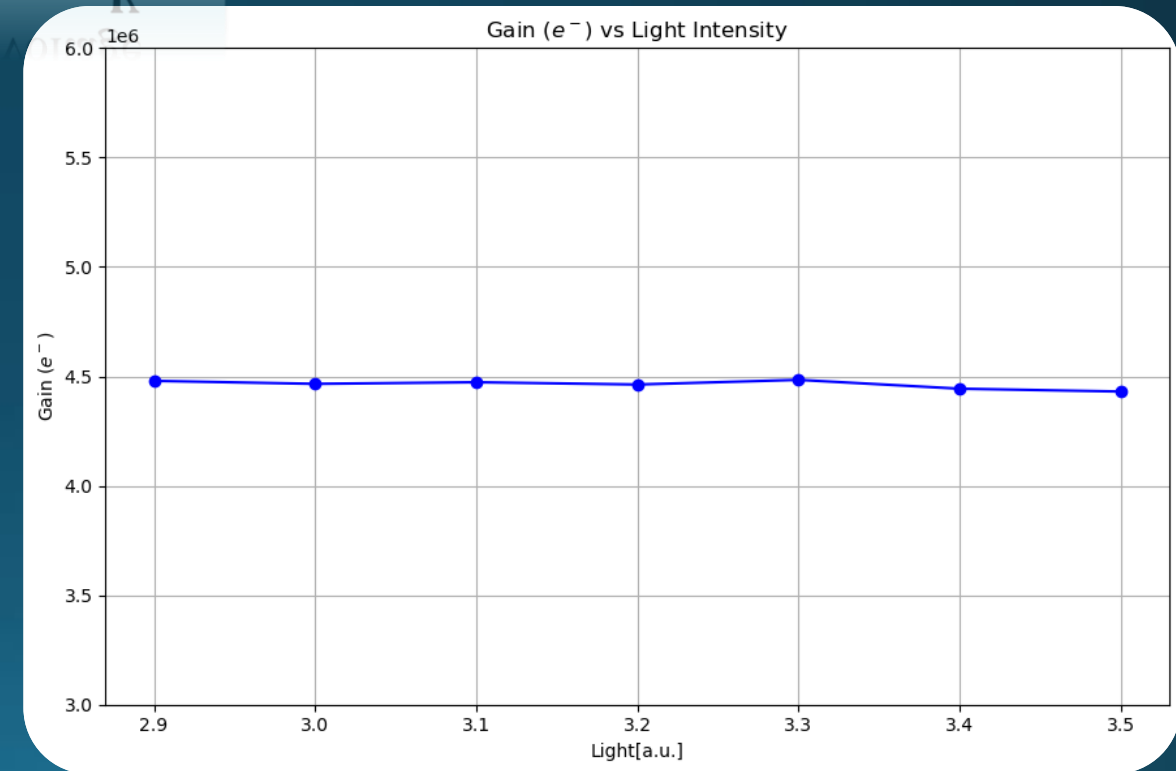
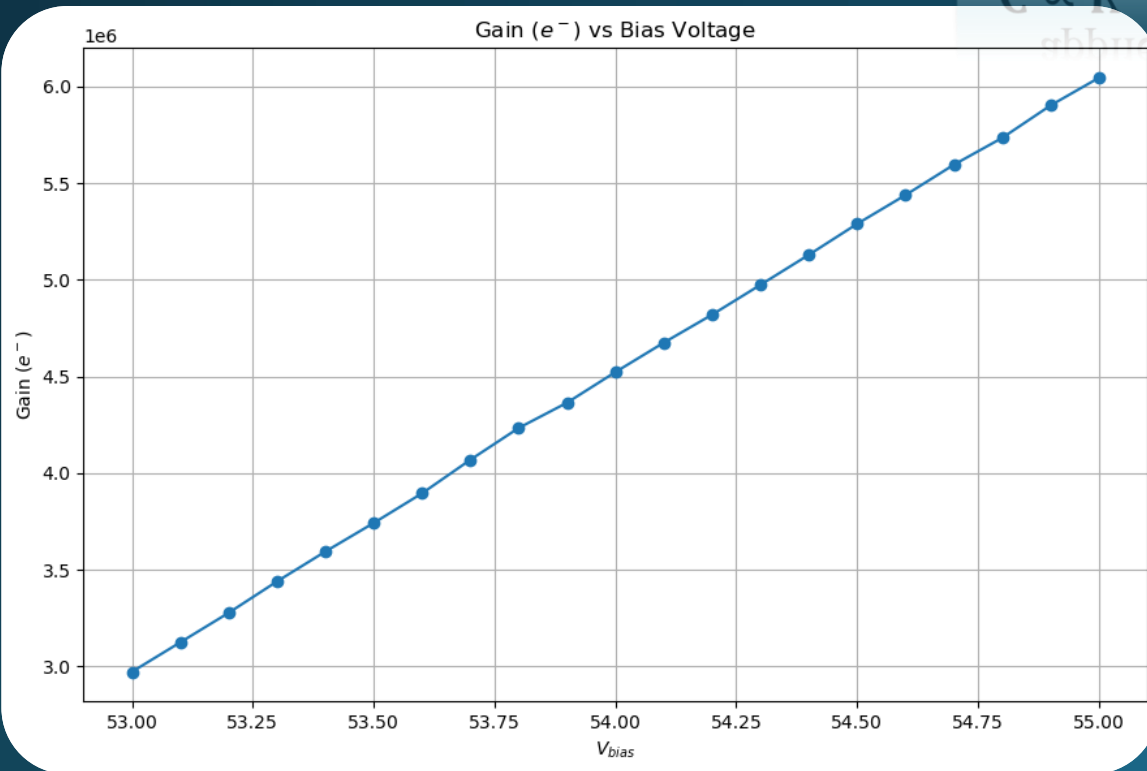
number of peaks
increasing



SiPM Avalanche Gain

It solely depends on the applied bias voltage

$$G \propto V_{ov} = V_{bias} - V_{bd}$$

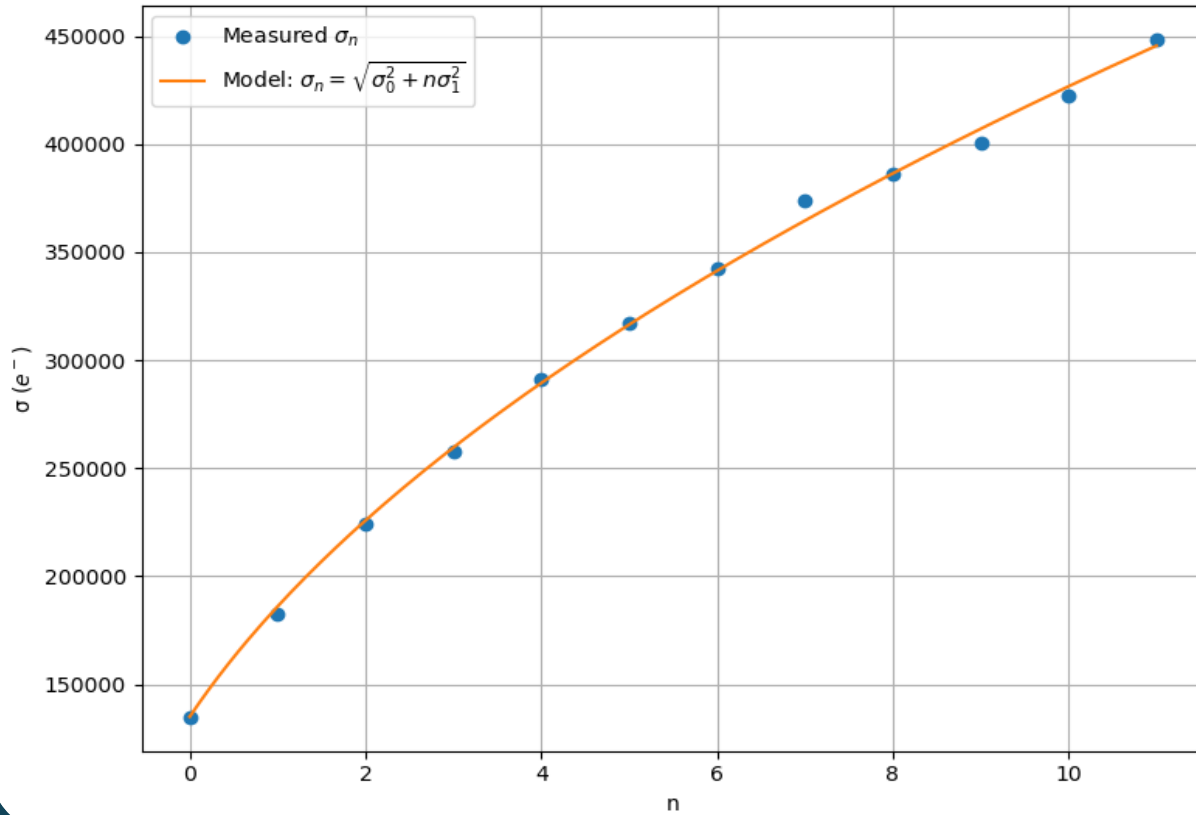


Standard Deviation & Variance

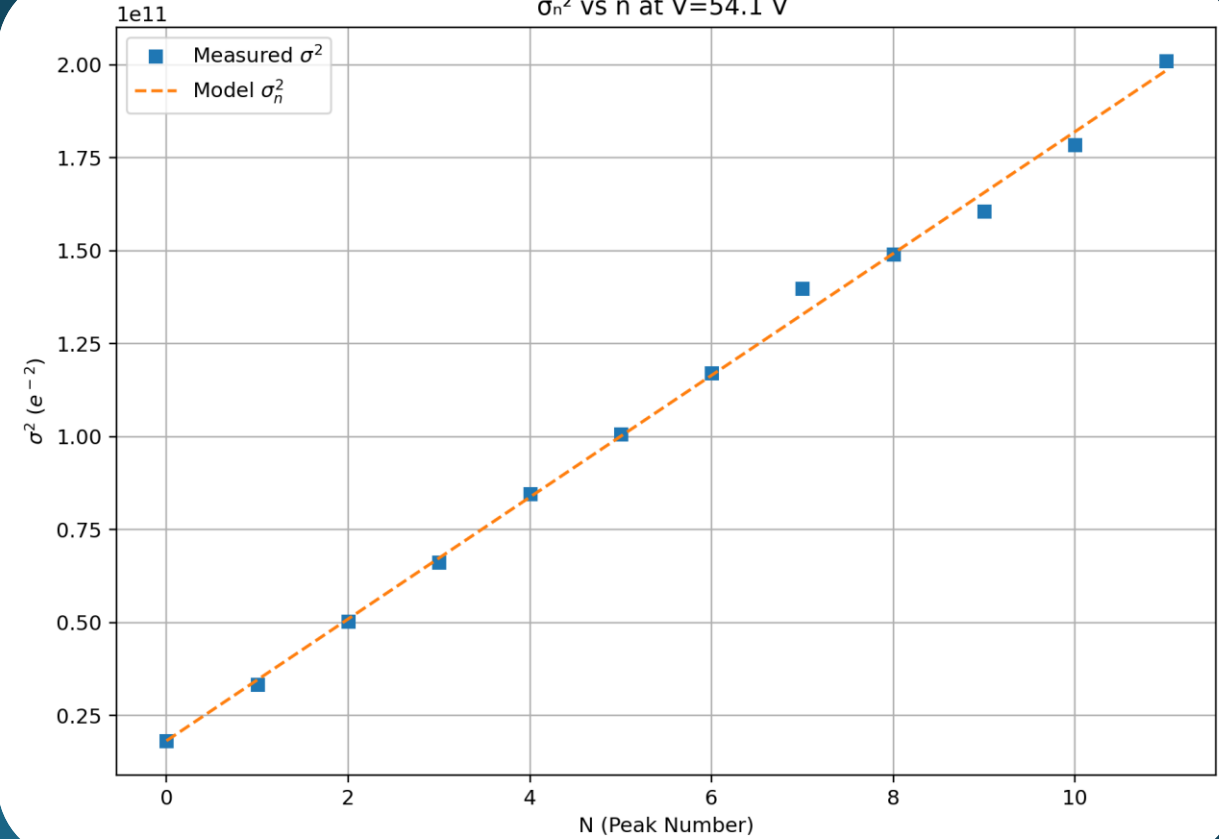
$$\sigma_n = \sqrt{\sigma_0^2 + n\sigma_1^2}$$

$$\sigma_n^2 = \sigma_0^2 + n\sigma_1^2$$

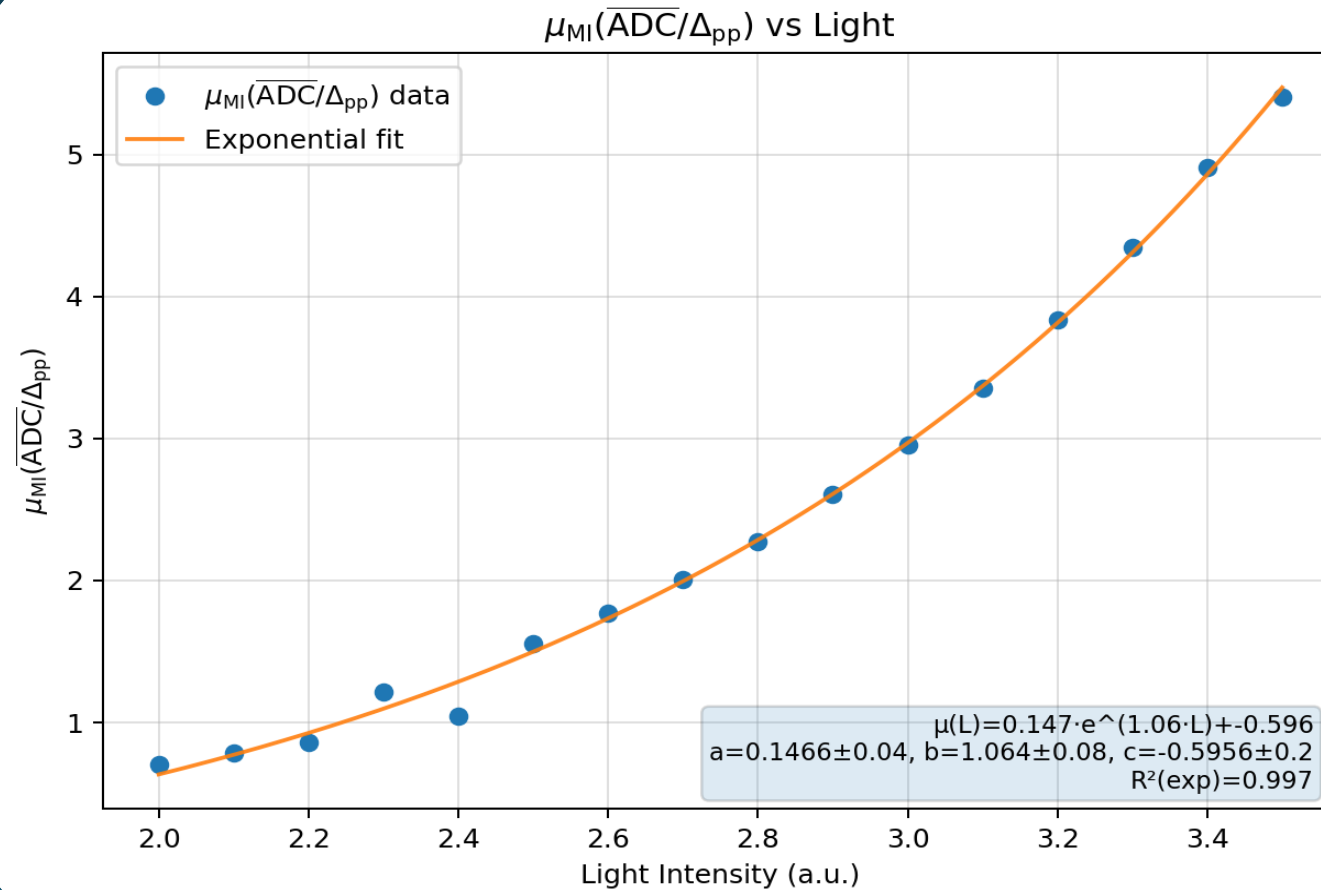
σ_n - Number of fired cells (n), V=54.1V



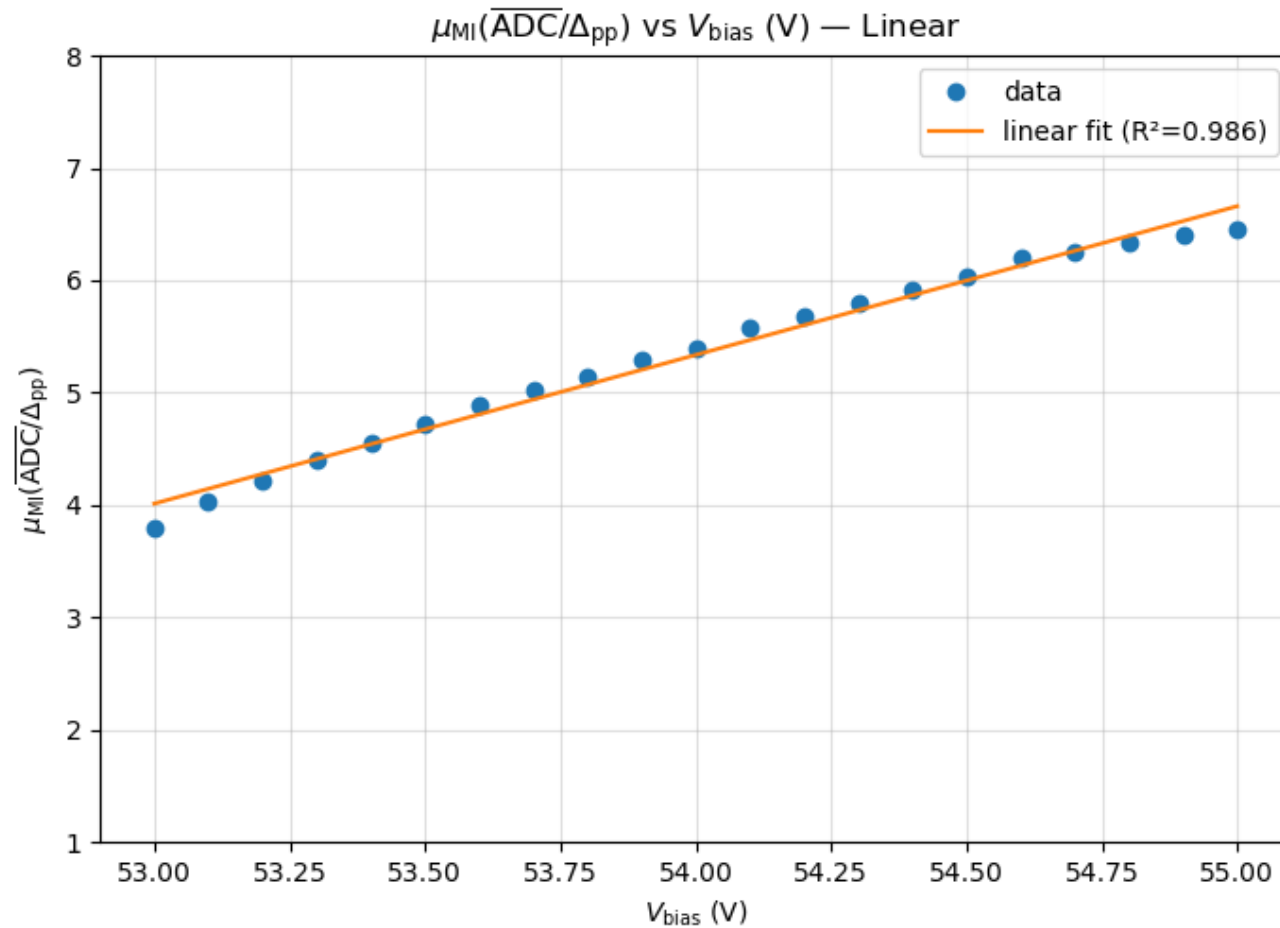
σ_n^2 vs n at V=54.1 V



Mean Number of Fired Cells (Detected Photons) as function of Light Intensity

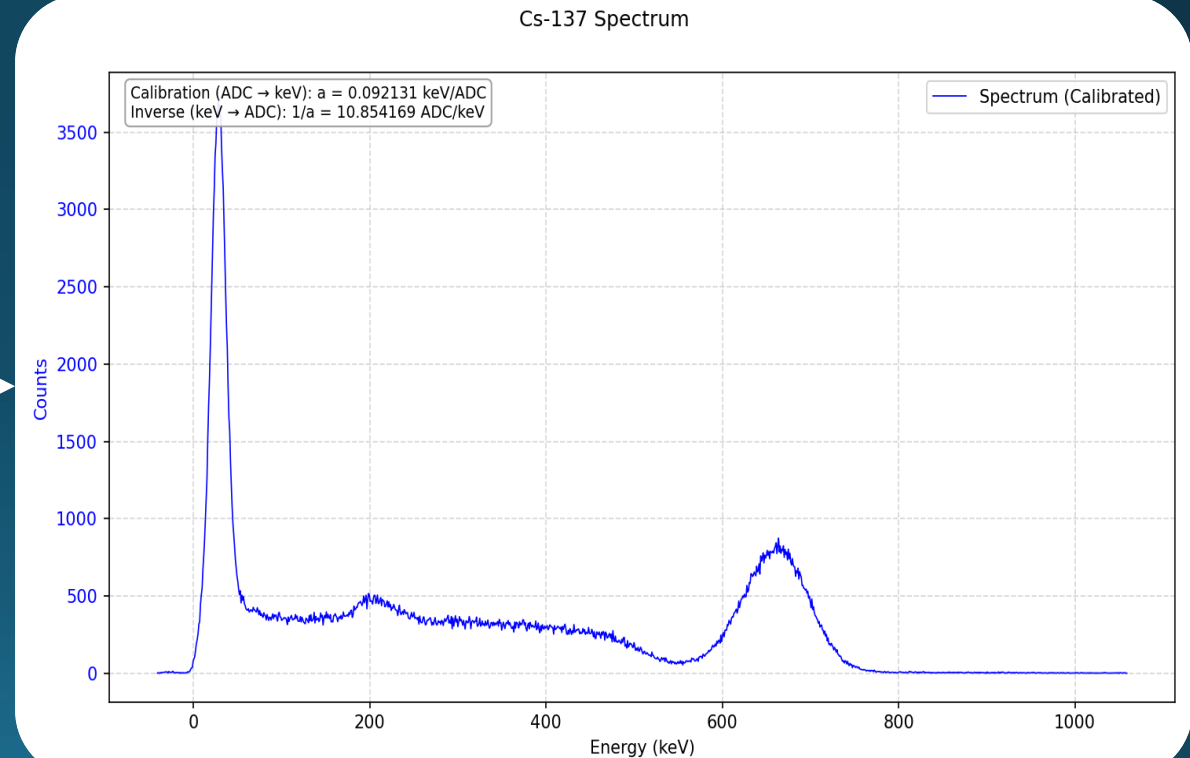
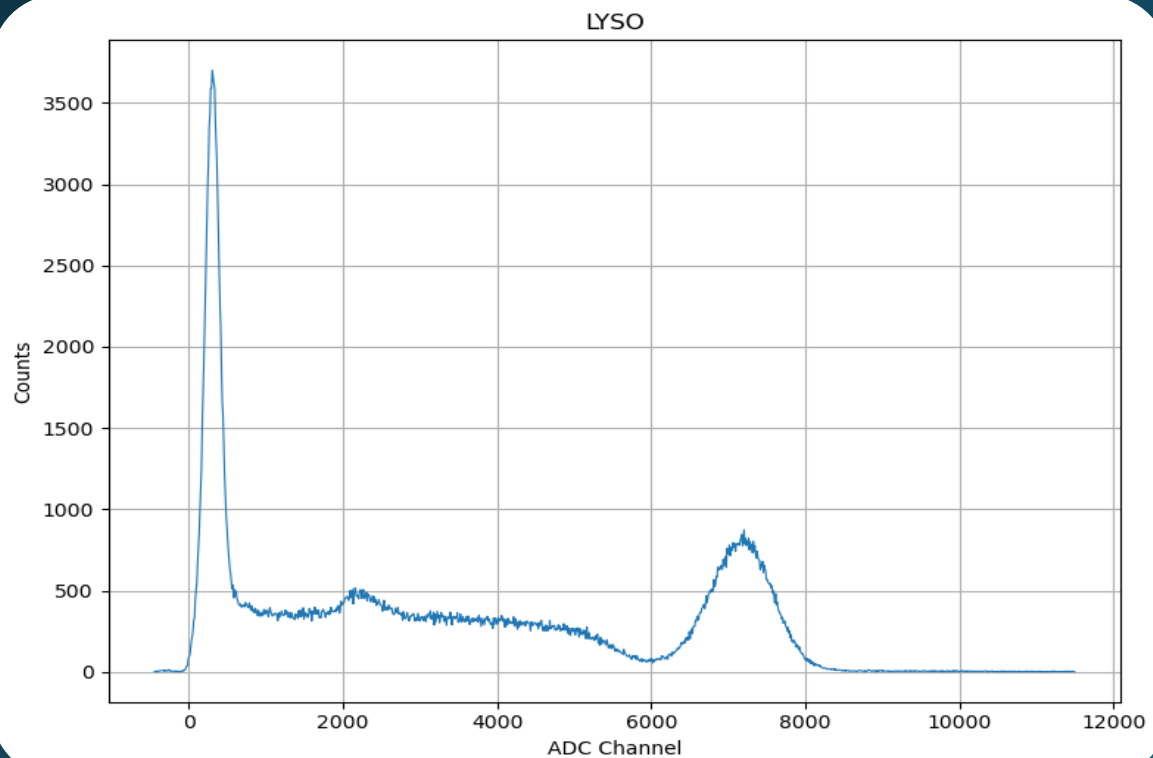


**Mean Number of
Fired Cells (Detected Photons)
as function of V_{bias}**

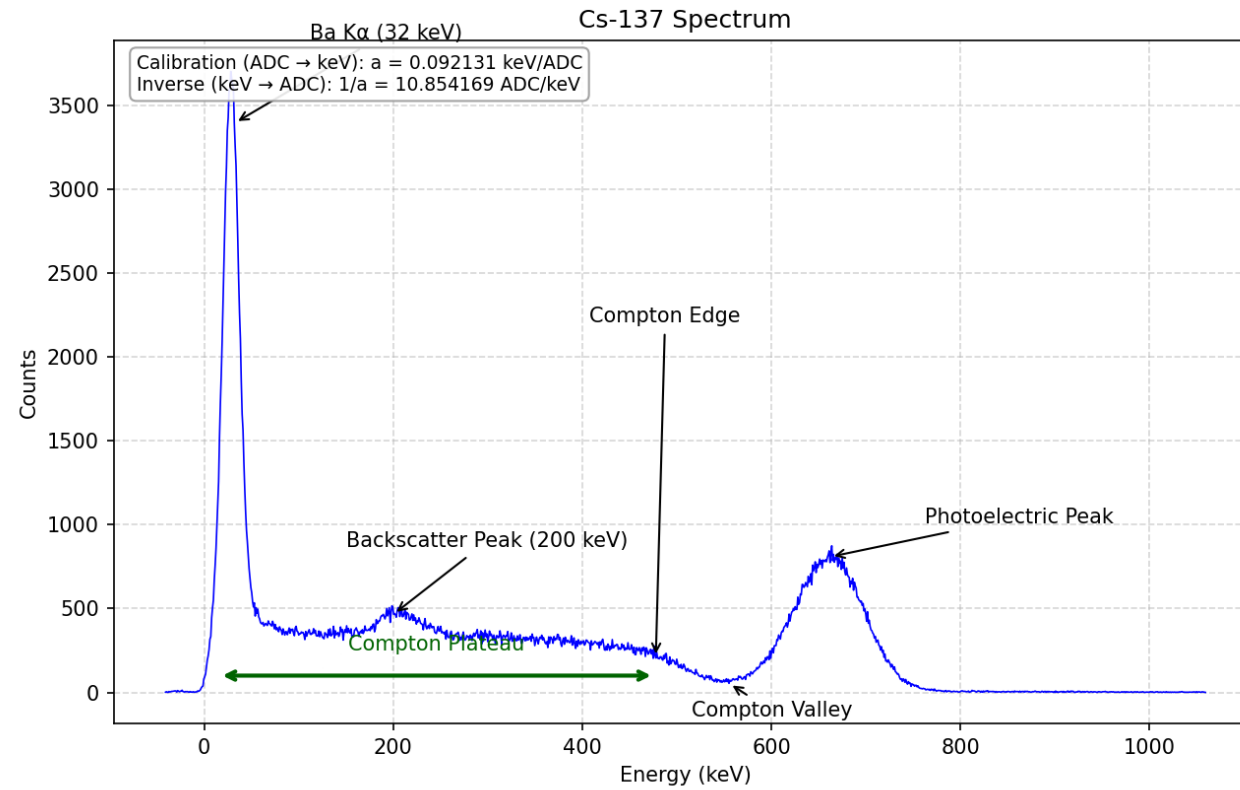


Radioactive Source Measurements [Cs-137]

Spectrum Calibration Use of the 662 keV γ -Photon

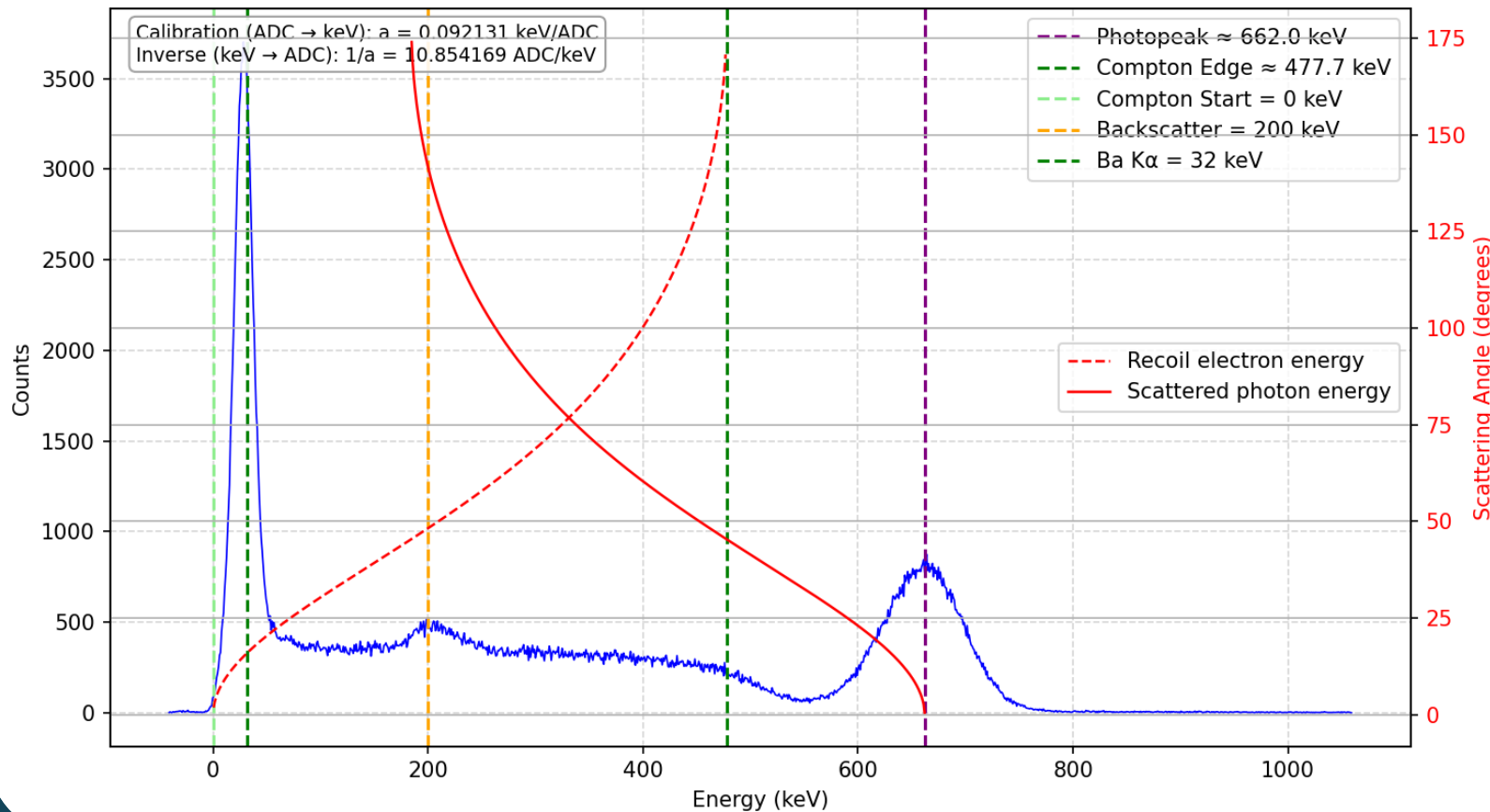


Peak Recognition



Spectrum Resolution

Cs-137 Spectrum
FWHM = 85.64 keV, Resolution = 12.94%



Scattered photon energy

$$E'_\gamma(\theta) = \frac{E_\gamma}{1 + \frac{E_\gamma}{mc^2} (1 - \cos \theta)}$$

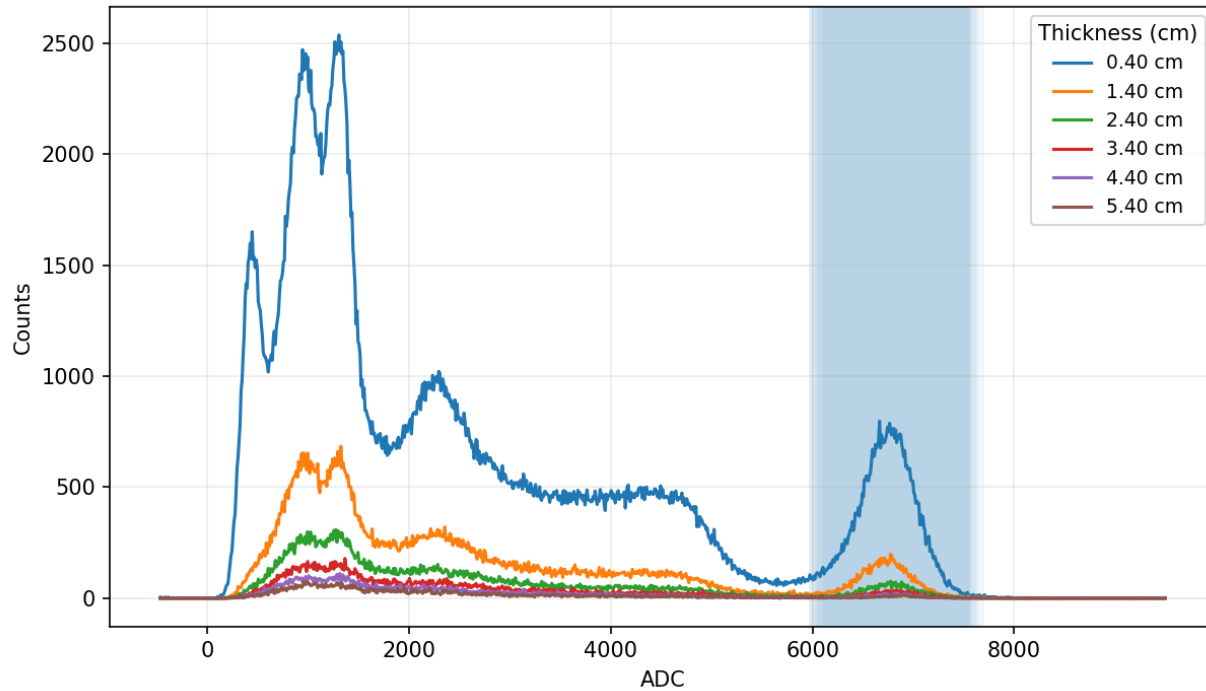
Recoil electron energy

$$K_e(\theta) = E_\gamma - E'_\gamma$$

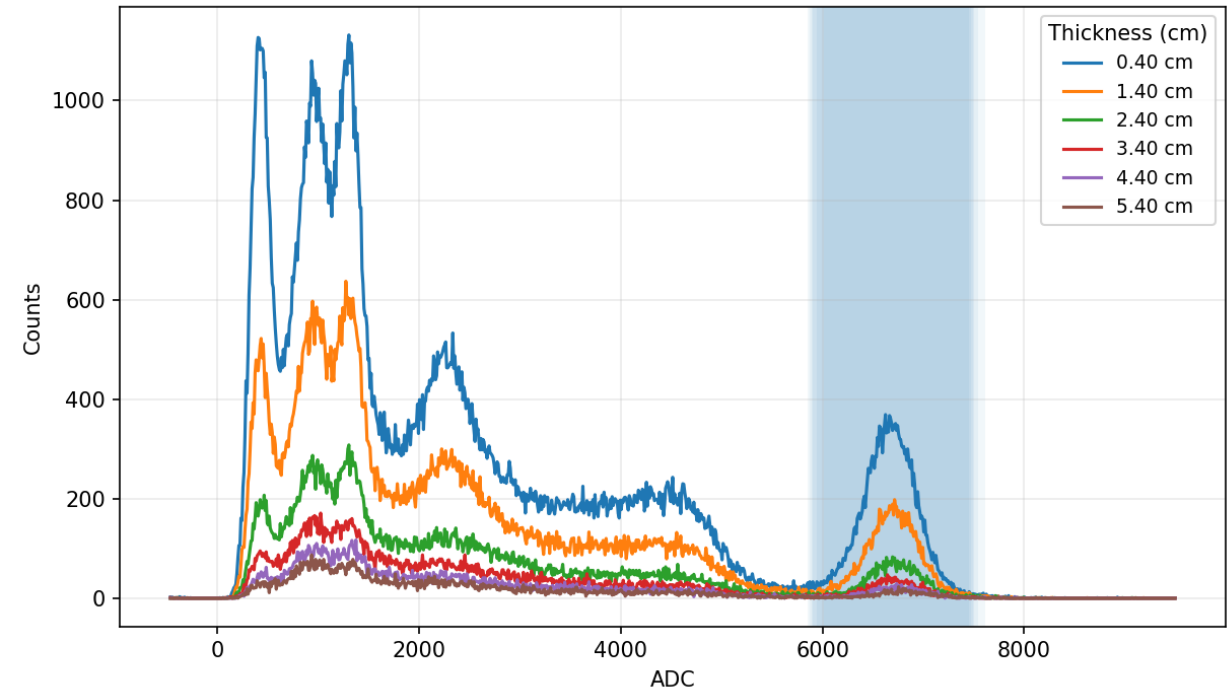
$$= E_\gamma \left(\frac{\frac{E_\gamma}{mc^2} (1 - \cos \theta)}{1 + \frac{E_\gamma}{mc^2} (1 - \cos \theta)} \right)$$

γ -Radiation Absorption

Gamma spectra with different absorber thicknesses-Aluminum



Gamma spectra with different absorber thicknesses-PMMA-Plexiglass



Exponential Absorption Law

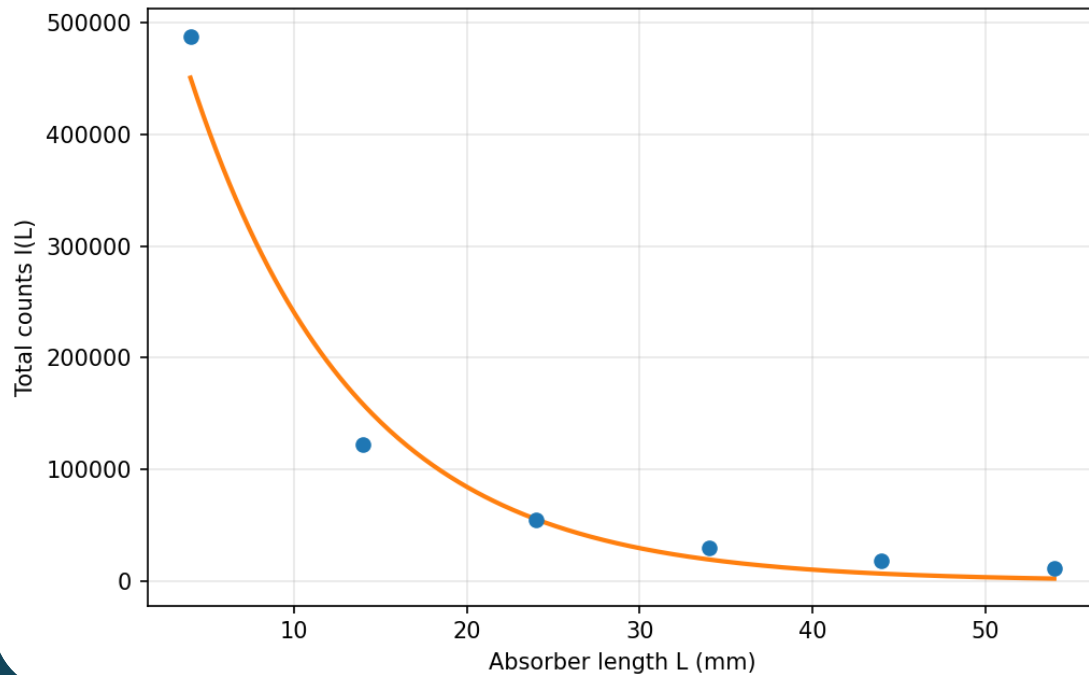
Applications:

- Material thickness measurement
- Unknown material identification through attenuation coefficient (μ)

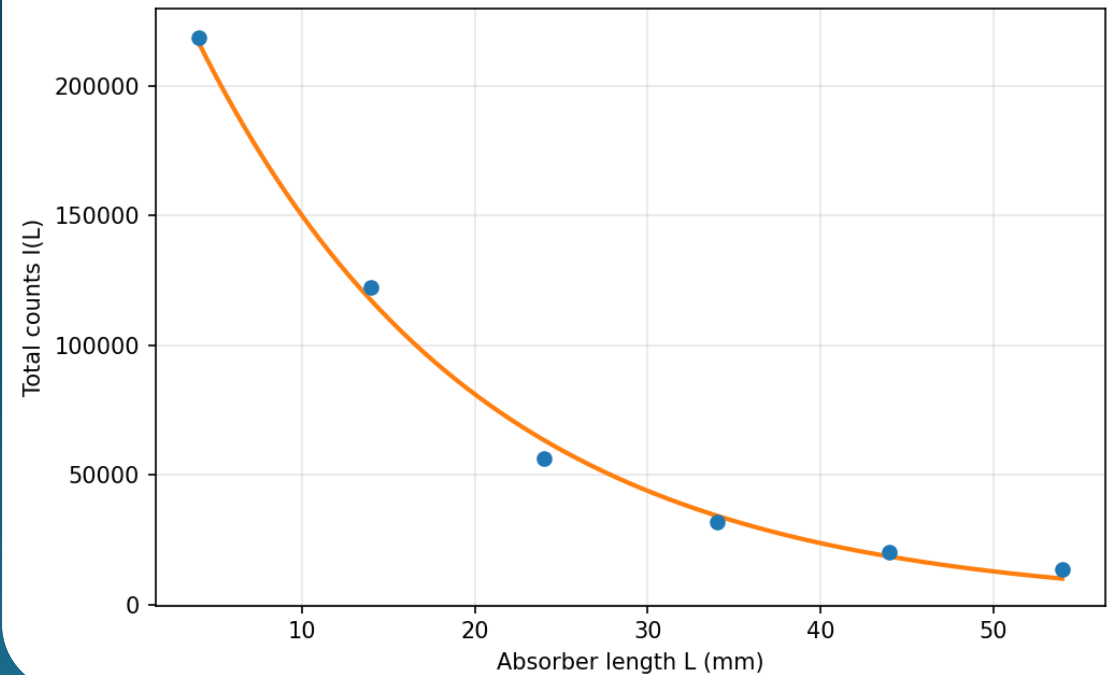
attenuation coefficient (μ)

Unknown material identification through

Aluminum — $I(L) = I_0 e^{-\mu L}$



Pmma Plexiglass — $I(L) = I_0 e^{-\mu L}$



Exploitation of Quantum Detection Randomness

Generation of a sequence of random numbers using experimental data, by harnessing the genuine **quantum randomness** in the number of detected photons during the SiPM experiment.

If x_n denotes the first number of the generated random sequence, then the next one is produced through the recursive relation:

$$x_{n+1} = f(x_n)$$

followed by a conversion into **binary** form for the final output (01110001...).

- **Verification of the randomness** of the generated number sequence through the **NIST Statistical Test Suite**
- **Utilization** of the resulting random sequence as an **input source** for **Monte Carlo simulations**, with accuracy up to more than **99%**

Test	Generated	Theoretical	Accuracy (%)
Monte Carlo π	3.146960	3.141593	99.829
European Call Price	8.871317	8.916037	99.498
Decay $N(T=150.0)$	154.920000	156.250000	99.668

- **Assembly of the Experimental Setup**

Complete integration of the SiPM, scintillator, electronics, and data-acquisition chain.

- **Measurements**

Systematic acquisition of spectra and charge histograms under controlled conditions (LED, radiation sources, varying bias & light intensity)

- **Characterization**

Extraction of key SiPM parameters (gain, PDE-related photon statistics, DCR, cross-talk, resolution).

- **Calibration**

ADC-to-charge and charge-to-photoelectron calibration enabling accurate quantitative analysis.

- **QRNG Implementation**

Utilization of photon-count randomness and SiPM avalanche statistics to generate and validate quantum-based random numbers.

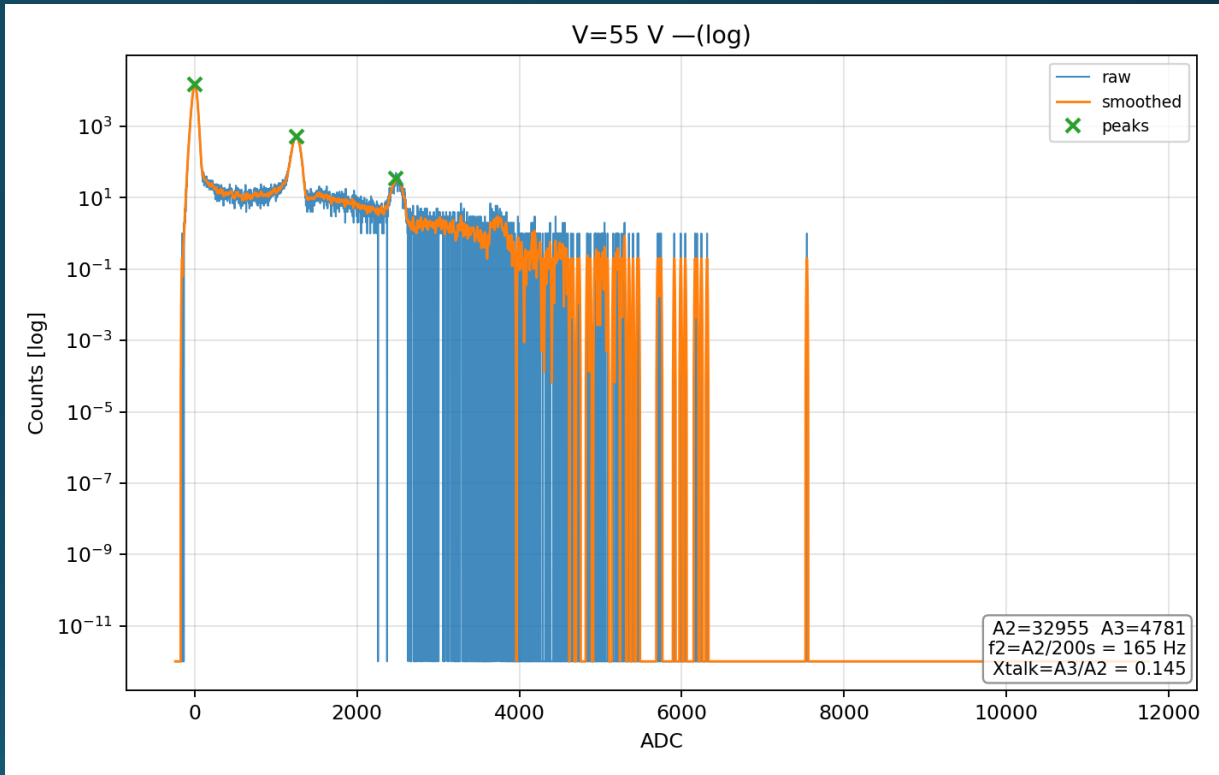
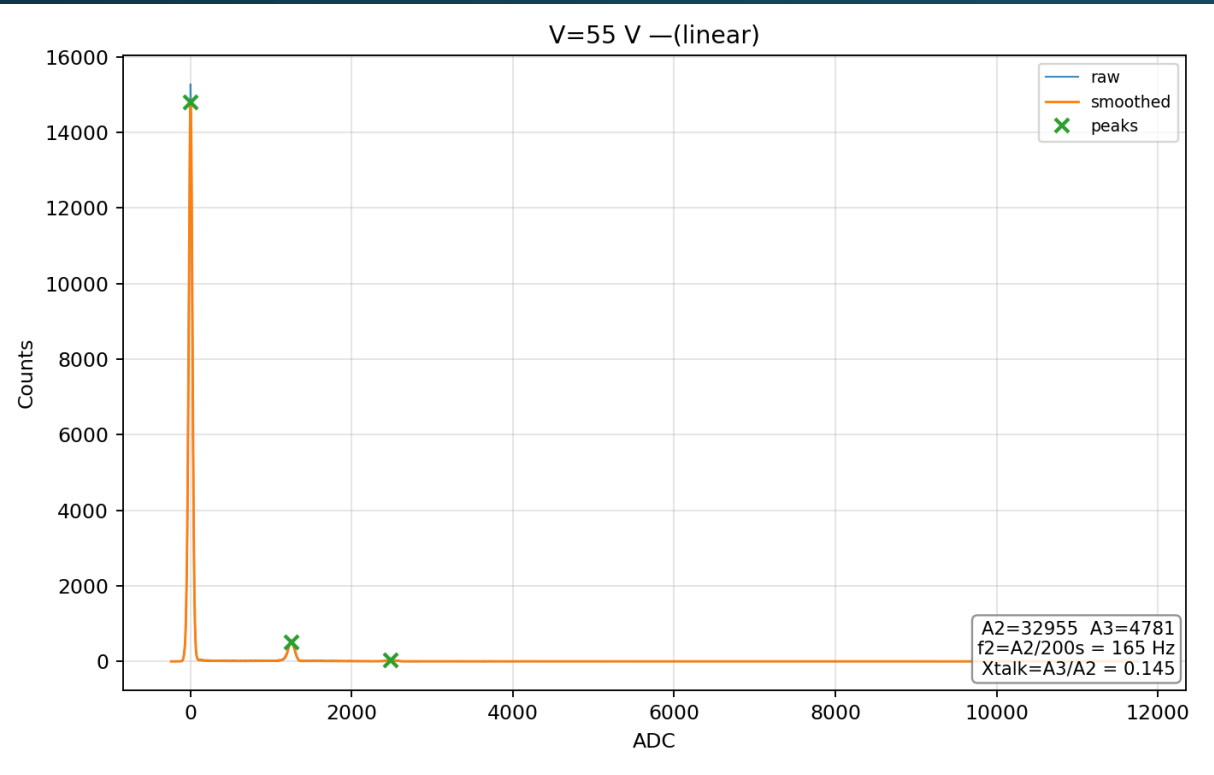
THANK YOU FOR YOUR ATTENTION

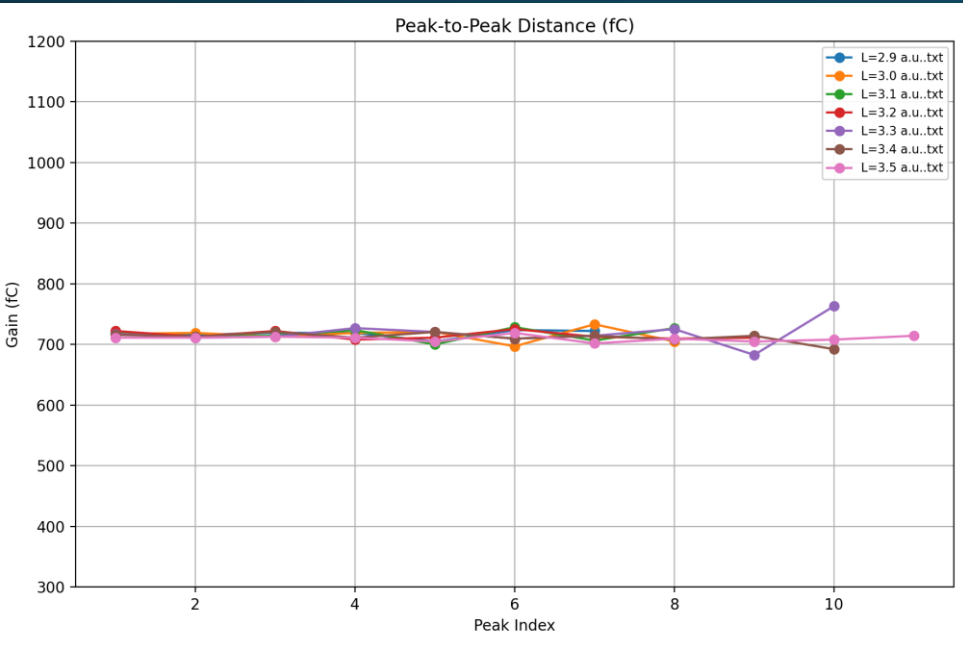
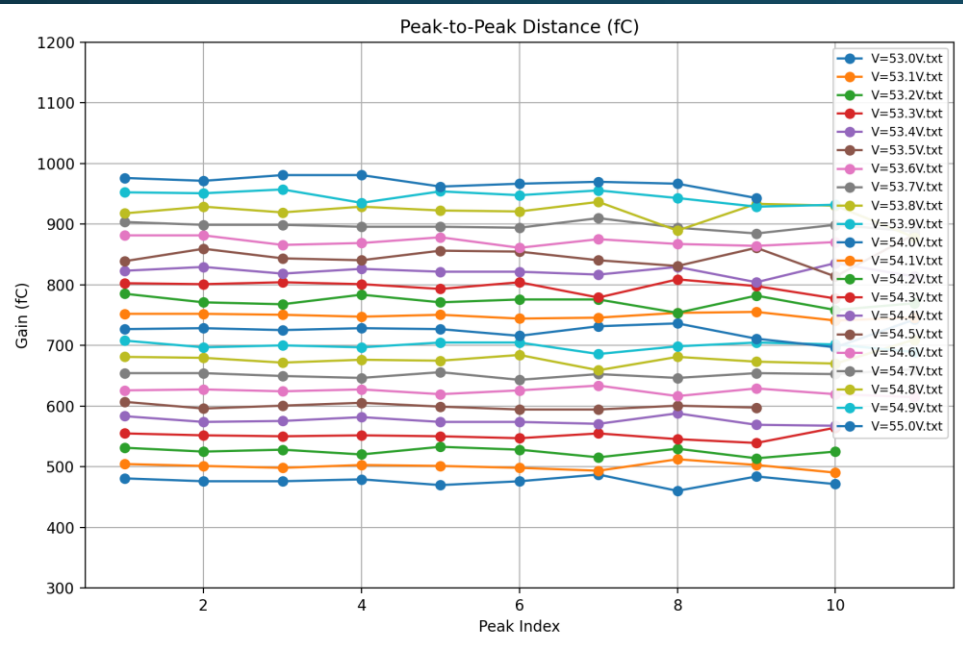
(QUESTIONS)

Supplementary Slides

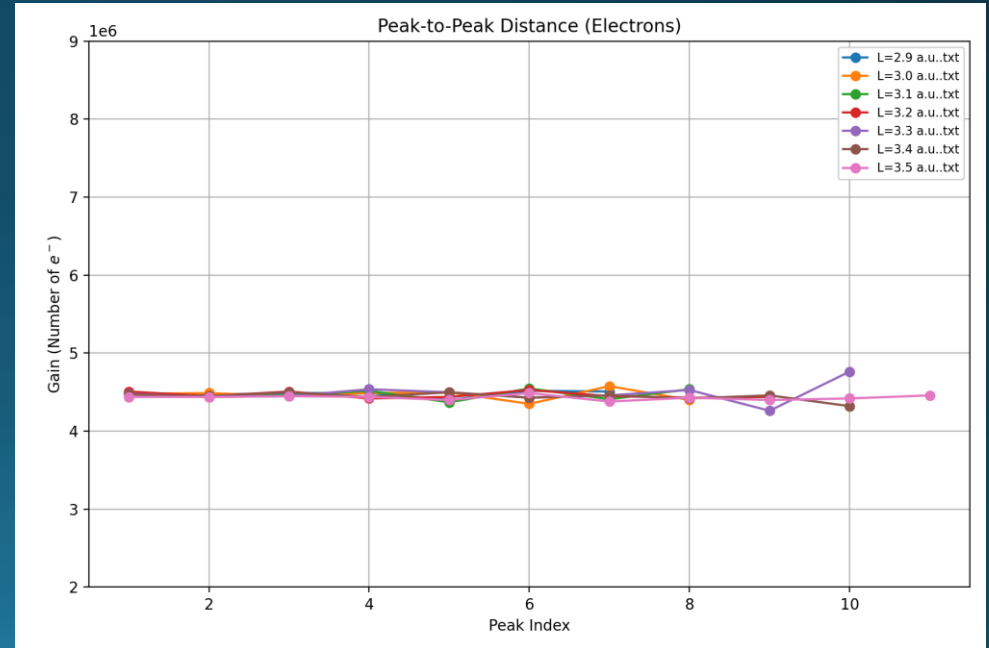
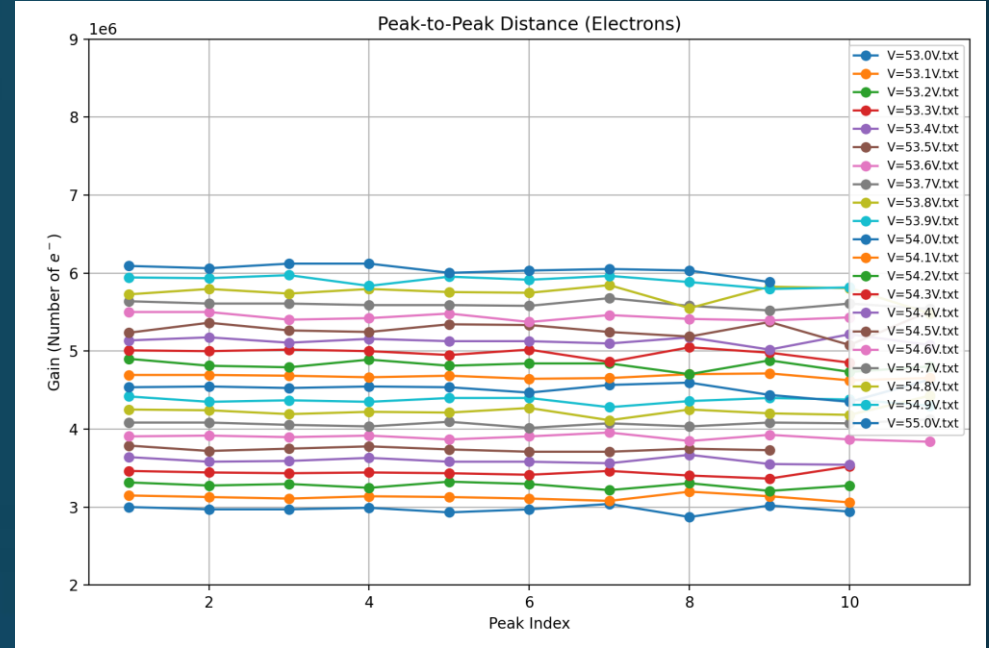
Key Parameters				
Voltages	Bias Voltage V_{bias}	Breakdown Voltage V_{bd}	Overvoltage $V_{ov} = V_{bias} - V_{bd}$	Turnoff Voltage V_{off}
Definition	The external voltage applied to the SiPM to operate its microcells	The minimum reverse bias voltage at which a microcell undergoes avalanche breakdown	The amount by which the bias voltage exceeds the breakdown voltage.	The voltage below which the avalanche process cannot be sustained and the device completely stops responding to light. Typically $V_{off} \cong V_{bd}$
Role	Determines the operating point of each microcell, influencing many of the detector's parameters	Critical for initiating Geiger-mode operation. Operating above this voltage allows microcells to detect single photons	Determines the gain and the probability of initiating an avalanche. Higher overvoltage generally increases gain but may also elevate dark count rates and noise.	Essential for quenching the avalanche and resetting the microcell for subsequent detections

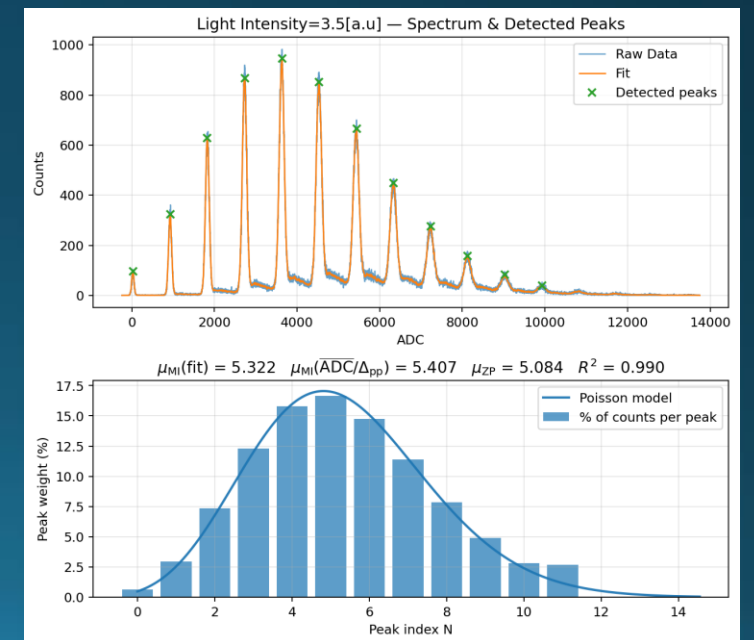
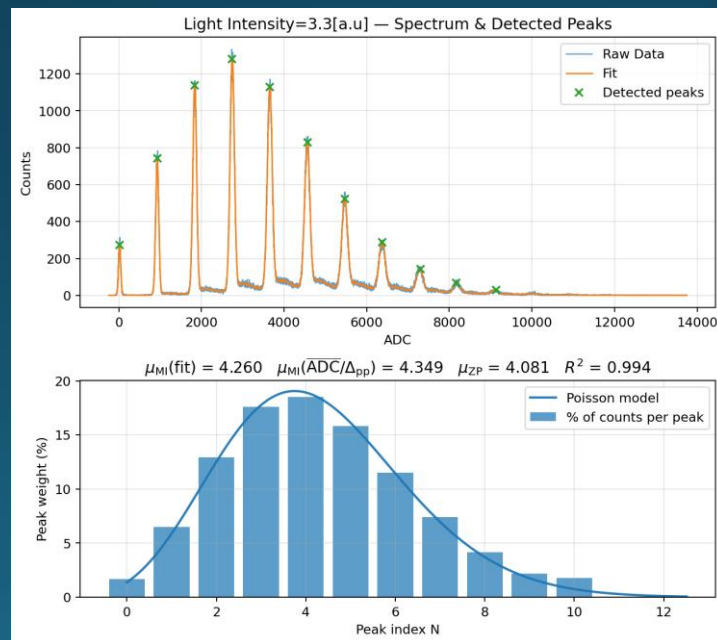
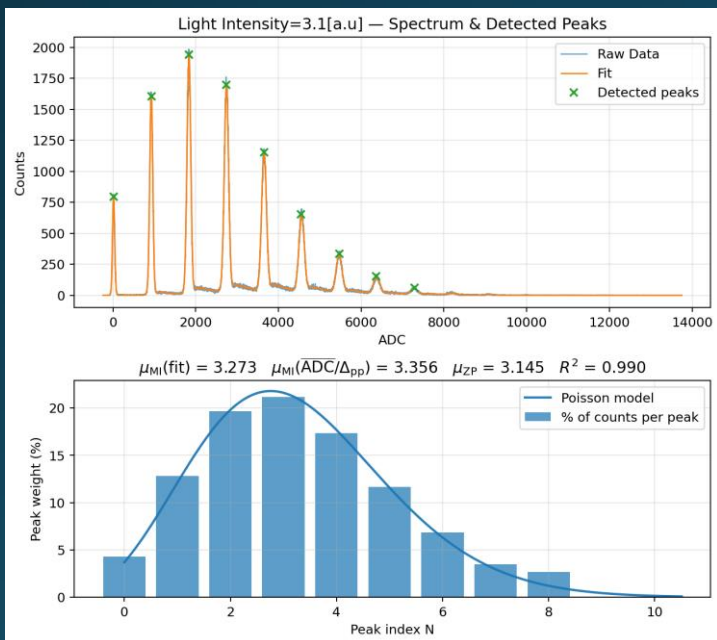
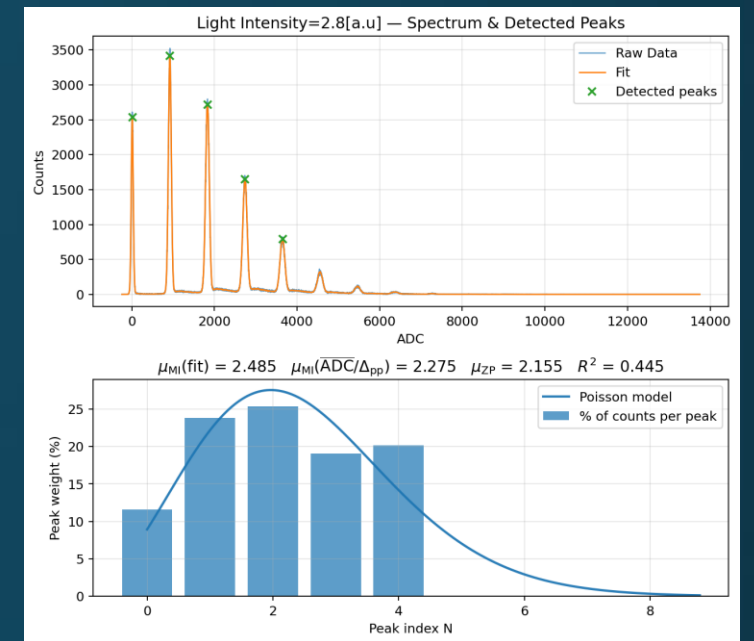
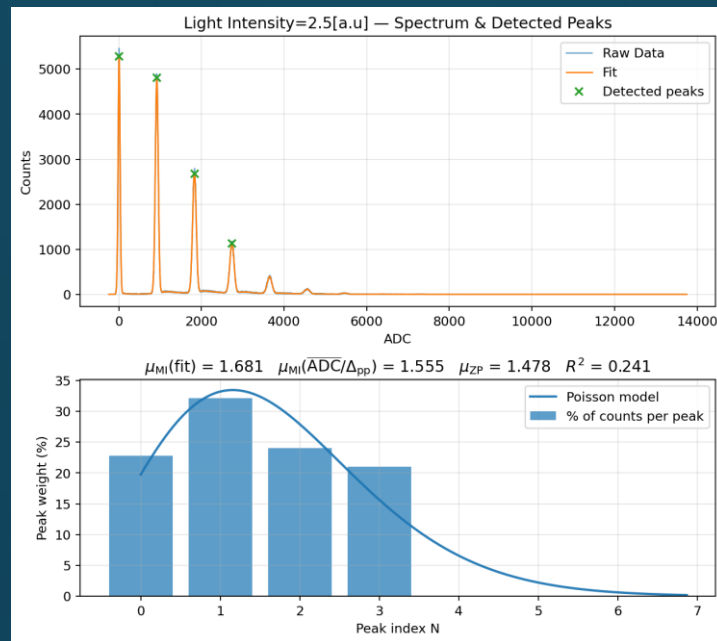
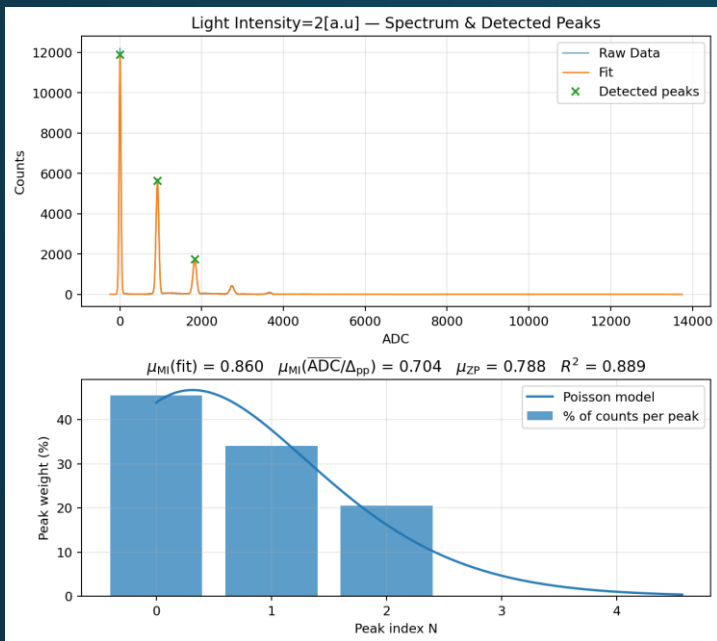
Key Parameters					
	Photon-Detection Efficiency	Gain	Cross-Talk	After-Pulse	DCR
Definition	$PDE = QE \cdot P_{av} \cdot FF$ <p>The probability that an incoming photon will be detected</p> <p>~(20 – 40)%</p>	<p>The amount of electrical charge generated per detected photon — essentially how much the initial signal is amplified</p> <p>$G \approx 10^6$</p>	<p>Delayed avalanches in the same microcell due to trapped carriers being released after the initial even — Carriers trapped in lattice defects during avalanche and later released</p>	<p>A photon emitted during an avalanche in one microcell may trigger a secondary avalanche in a neighboring cell — Internal photon emission during carrier recombination</p>	<p>The rate at which microcells fire spontaneously (without photon input) due to thermal excitation or tunneling</p>
Role	<p>A measure of sensitivity. Higher PDE means more efficient photon detection — critical for low-light applications</p>	<p>Determines the amplitude of the output signal; crucial for digitizing and quantifying light intensity</p>	<p>Creates false secondary pulses; degrades timing resolution and distorts pulse shape</p>	<p>Leads to overestimation of the number of detected photons; worsens resolution and introduces non-linearity</p>	<p>Acts as a form of background noise; high DCR reduces the signal-to-noise ratio and can mimic real photon events</p>

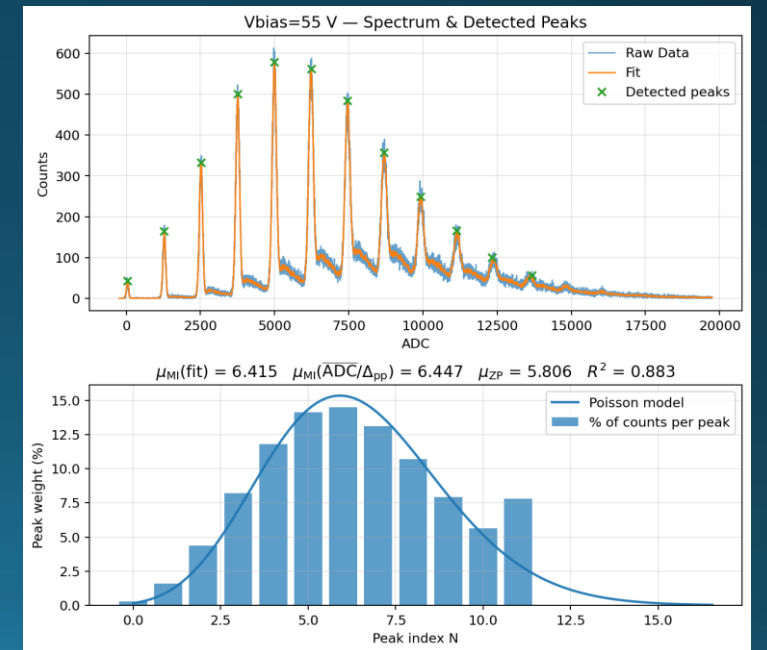
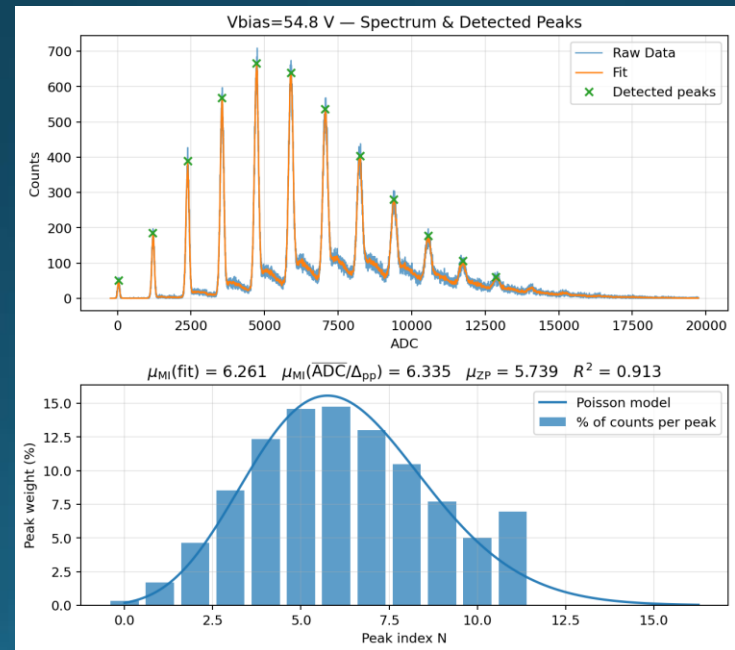
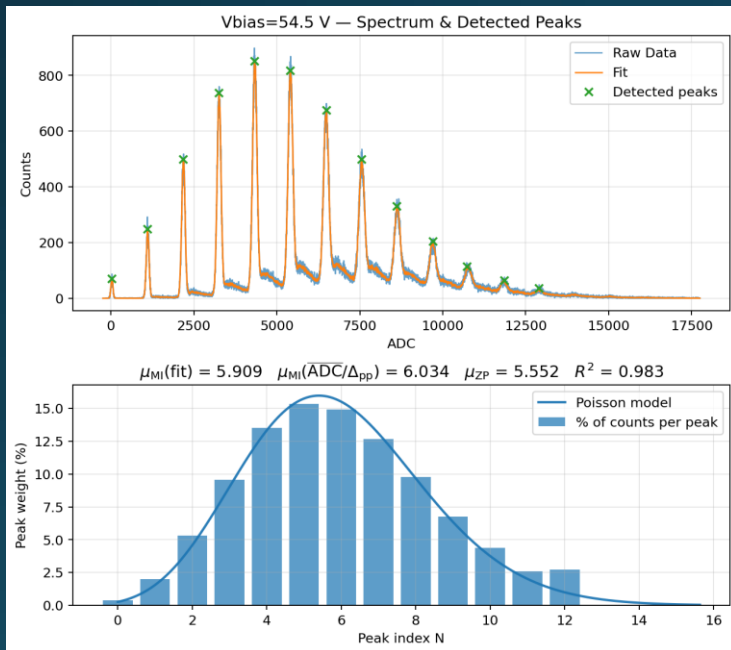
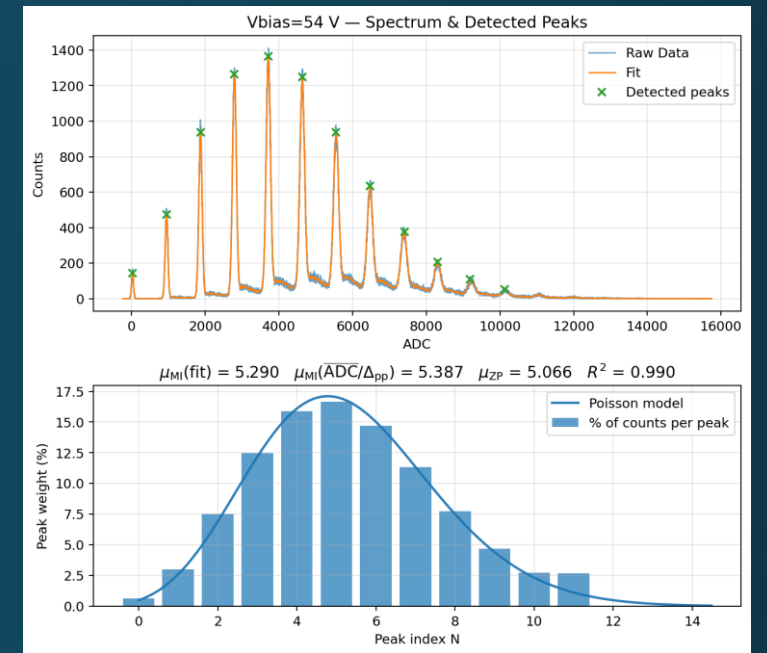
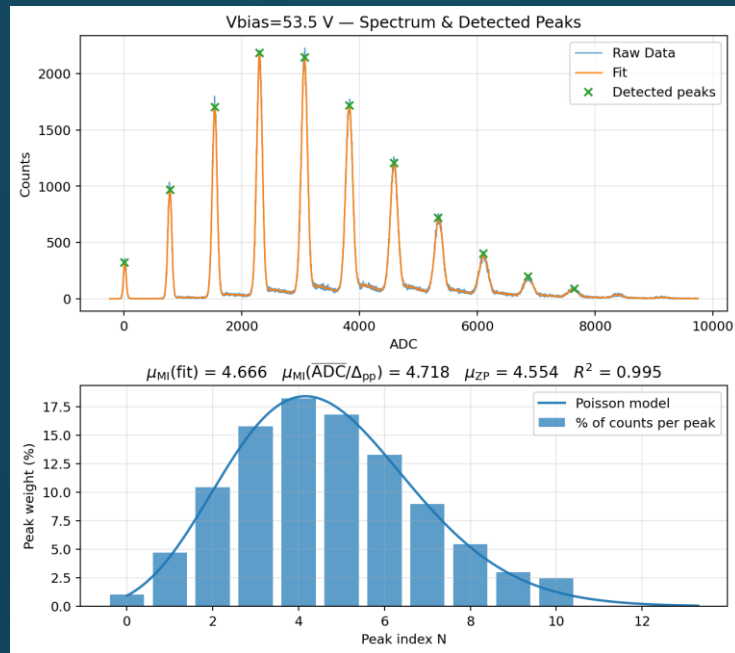
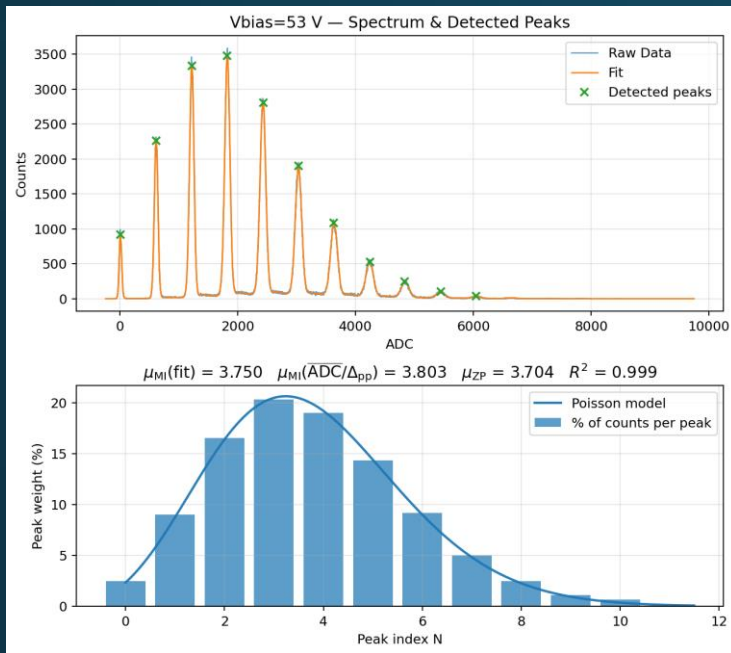




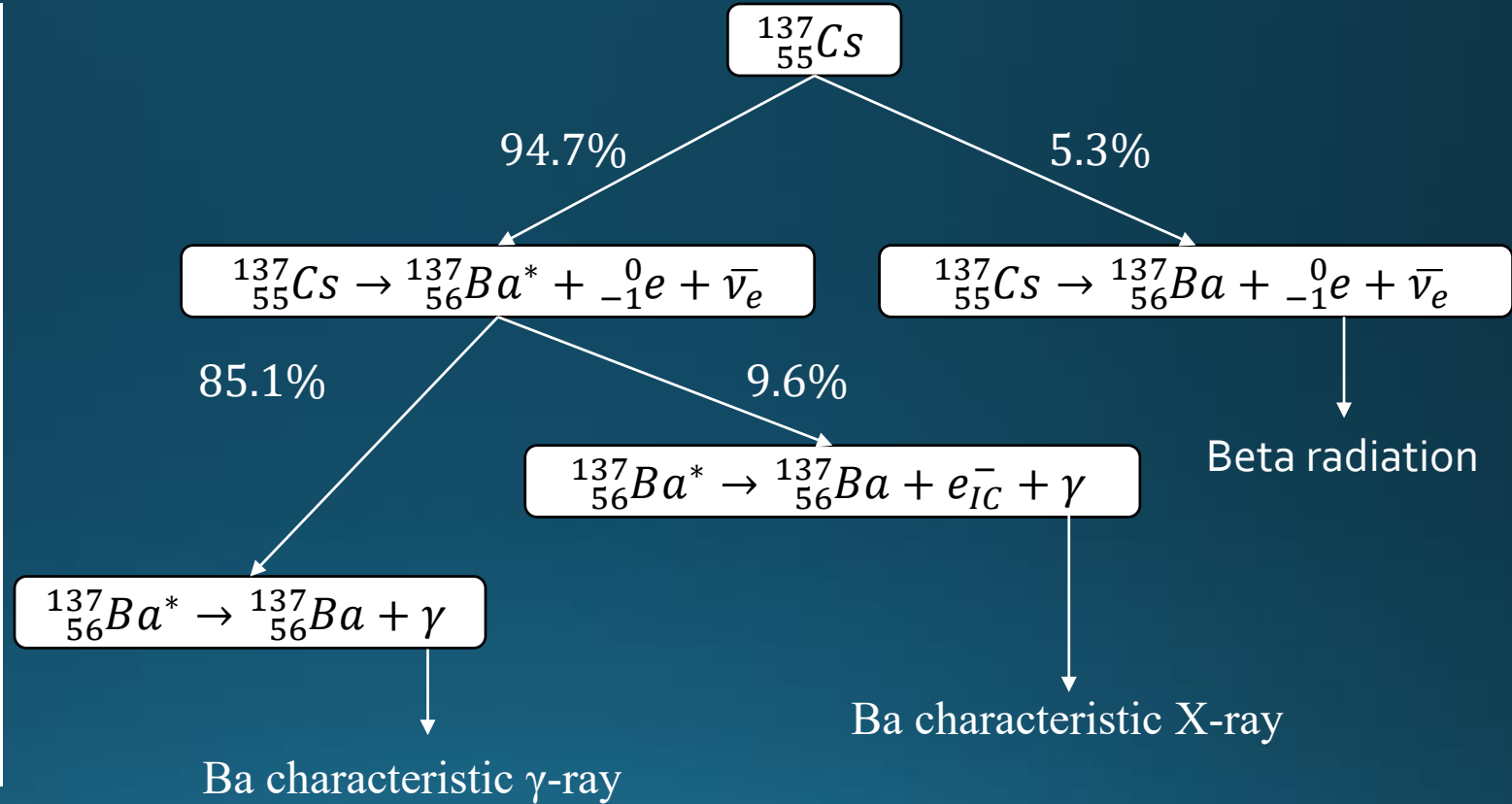
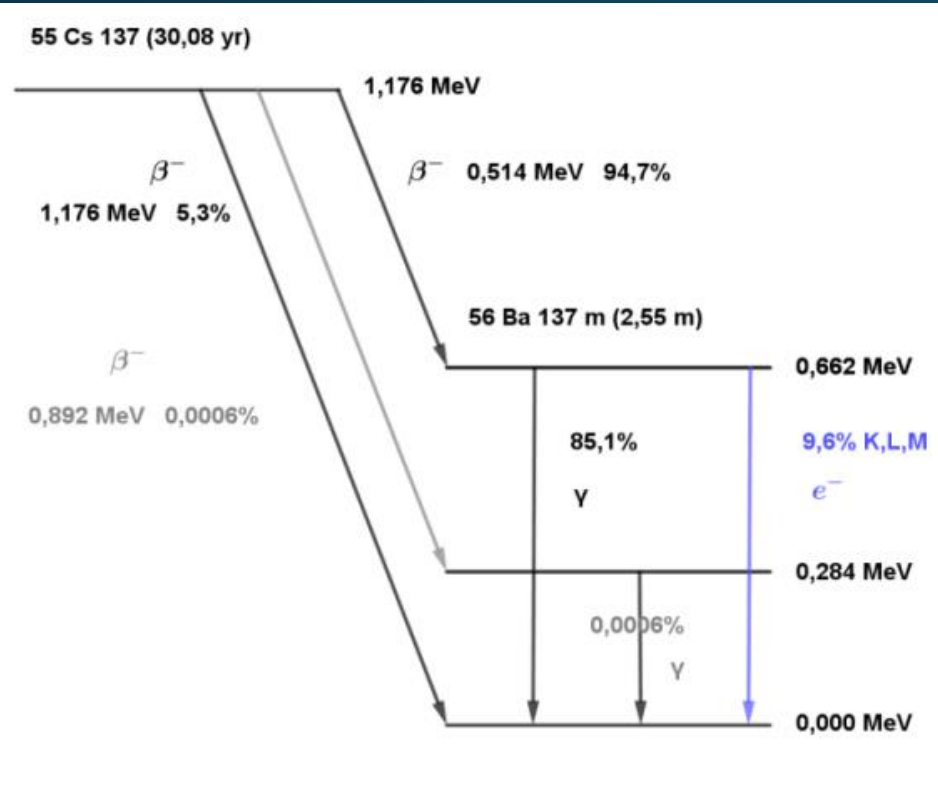
SiPM Avalanche Gain







Cs-137 Decay



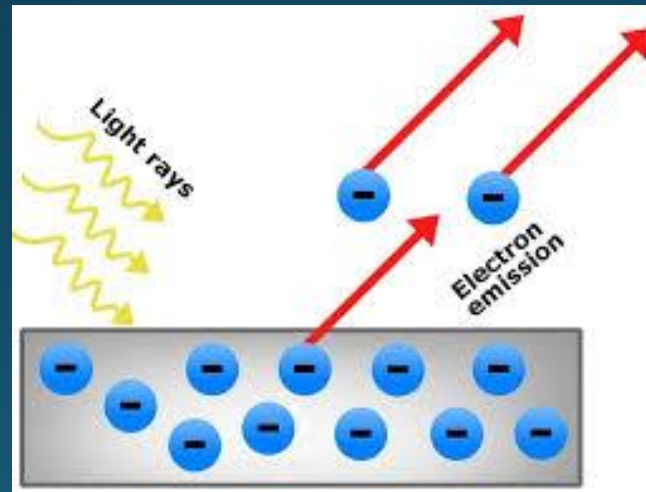
Photoelectric Effect

Incident Gamma Photon Energy

$$E_0 = 662keV$$

Dominant at energy less than 100Kev

$$\gamma + atom \rightarrow ion + e^{-}$$



$$E_e = E_\gamma - E_b = 662 - E_b$$